TEXAS INSTRUMENTS

TPA3139D2 10W ステレオ、3.5V～14.4V、低アイドル電流、インダクタレスのクラス D アンプ

1 特長

- 2 × 3W (8Ω 負荷、1% THD+N、7.4V 電源)
- 2 × 10W (8Ω 負荷、1% THD+N、13.5V 電源)
- 高速な電源オン時間：15ms 未満
- 広い電源電圧範囲：3.5V～14.4V
  –
- 小さいアイドル電流と小型フットプリントにより、携帯オーディオ・アプリケーションに好適
  - 4 × 4mm2 の QFN-24 パッケージ
  - 1SPW 変調で 20mA (12V) のアイドル電流
  - 90% を超える Class-D 効率
- 柔軟なオーディオ・ソリューション
  - MUTE 信号による高速なイネーブルと、出力のイネーブル
  - シングルエンドまたは差動アナログ入力
  - ゲインを選択可能：20dB、26dB
- 保護および自動復元機能を内蔵
  - ピン間、ピンからグランド、ピンから電源への短絡保護
  - サーマル保護、低電圧保護、過電圧保護
  - 電力リミッタおよび DC スピーカ保護
- 拡散スペクトラム変調により EMI 放射を低減
- ソリューションのサイズとコストを低減
  - フェライト・ビーズ・フィルタを使用して EN55022 EMC に準拠
  - 外部ヒートシンク不要

2 アプリケーション

- モバイル、携帯ラジオ
- ノートブック PC
- Bluetooth® スピーカ、ワイヤレス・スピーカ
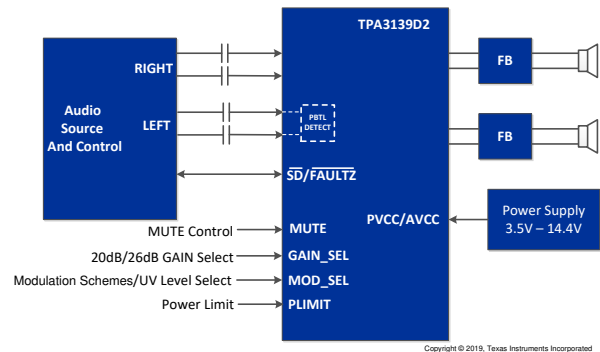- スマート家電
- テレビ、モニタ

3 概要

TPA3139D2 は 10W ステレオの Class-D オーディオ・アンプであり、15ms 未満の短い電源オン時間とミュート機能を特長としています。わずか 20mA (12V) のアイドル電流しか消費せず、最低 3.5V で動作できるため、長時間のオーディオ再生が可能です。TPA3139D2 は小さな 4 × 4mm^2 の QFN パッケージを採用していることに加えて、スペースの制約が厳しい 2 セルまたは 3 セル・バッテリで動作するシステムに最適化されています。さらに拡散スペクトラム制御により、EMC 要件を満たしながら安価なフェライト・ビーズ・フィルタを使用できるため、システム・コストを削減できます。

設計をより簡素化するために、TPA3139D2 は低電圧、過電圧、電力制限、短絡、過熱などの基本的な保護機能に加えて、DC スピーカ保護機能を内蔵しています。これらの保護機能はすべて自動復帰をサポートしています。

製品情報[(1)]

部品番号	パッケージ	本体サイズ (公称)
TPA3139D2	VQFN (24)	4.0mm × 4.0mm

(1) 利用可能なすべてのパッケージについては、このデータシートの末尾にある注文情報を参照してください。

概略回路図

Table of Contents

4 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Changes from Revision * (October 2019) to Revision A (August 2020)   **Page**

• Added note [4] to T$_A$ in the *Recommended Operating Condition* 6

Device Comparison Table

Product	Supply Voltage	Modulation Scheme	Package	R$_{(ds)}$on	Gain	Inductor Free
TPA3139D2	3.5-V to 14.4-V	BD, 1SPW	VQFN-24	180-mΩ	20-dB, 26-dB	YES
TPA3138D2	3.5-V to 14.4-V	BD, 1SPW	HTSSOP-28	180-mΩ	20-dB, 26-dB	YES
TPA3110D2	8-V to 26-V	BD	HTSSOP-28	240-mΩ	20-dB, 26-dB, 32-dB, 36-dB	NO
TPA3136D2	4.5-V to 14.4-V	BD	HTSSOP-28	240-mΩ	26-dB	YES
TPA3136AD2	8-V to 14.4-V	BD	HTSSOP-28	240-mΩ	26-dB	YES

5 Pin Configuration and Functions
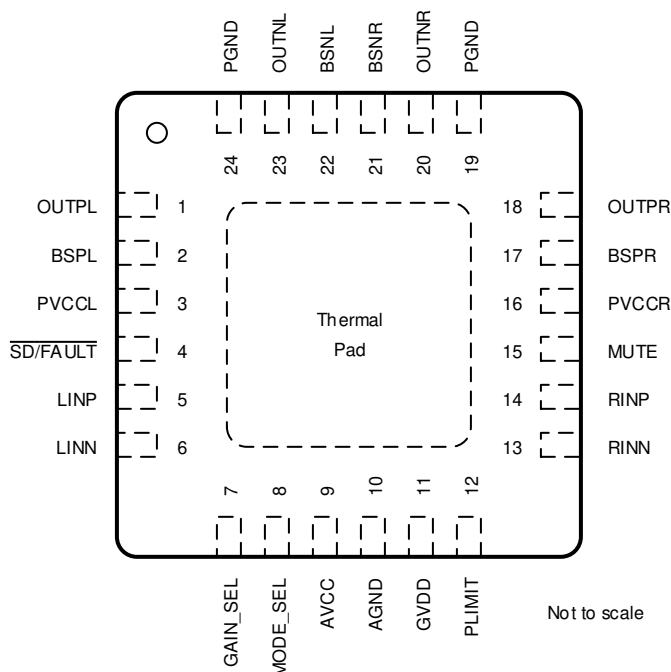
図 5-1. RGE Package, 24-Pin VQFN, (Top View)

Pin Functions

NAME	NO.	I/O/P[1]	DESCRIPTION
OUTPL	1	O	Class-D H-bridge positive output for left channel.
BSPL	2	P	Bootstrap supply (BST) for positive high-side FET of the left channel.
PVCCL	3	P	Power supply for left channel H-bridge. Right channel and left channel power supply inputs are connected internally.
SD/FAULT	4	IO	TTL logic levels with compliance to AVCC. Shutdown logic input for audio amp (LOW, outputs Hi-Z; HIGH, outputs enabled). General fault reporting includes Over-Temp, Over-Current, and DC Detect. SD/FAULT= High, normal operation, SD/FAULT= Low, fault condition. Device will auto-recover once the OT/OC/DC Fault has been removed.
LINP	5	I	Positive audio input for left channel. Biased at 2.5 V. Connect to GND for PBTL mode.
LINN	6	I	Negative audio input for left channel. Biased at 2.5 V. Connect to GND for PBTL mode.
GAIN_SEL	7	I	Gain select least significant bit. TTL logic levels with compliance to AVDD. Low = 20-dB Gain, High = 26-dB Gain, Floating = 26-dB Gain.
MODE_SEL	8	I	Mode select least significant bit. TTL logic levels with compliance to AVDD. Low = BD Mode with UV Threshold = 7.5 V, High = 1SPW Mode with UV Threshold = 3.4V, Floating = 1SPW Mode with UV threshold = 3.4V.
AVCC	9	P	Analog supply.

PIN		I/O/P[1]	DESCRIPTION
NAME	NO.		
AGND	10	P	Analog signal ground.
GVDD	11	O	FET gate drive supply. Nominal voltage is 5 V.
PLIMIT	12	I	Power limiter level control. Connect a resistor divider from GVDD to GND to set power limit. Connect directly to GVDD for no power limit.
RINN	13	I	Negative audio input for right channel. Biased at 2.5 V.
RINP	14	I	Positive audio input for right channel. Biased at 2.5 V.
MUTE	15	I	Mute signal for fast disable/enable of outputs (HIGH = outputs Hi-Z, LOW = outputs enabled). TTL logic levels with compliance to AVCC.
PVCCR	16	P	Power supply for right channel H-bridge. Right channel and left channel power supply inputs are connected internally.
BSPR	17	P	Bootstrap supply (BST) for positive high-side FET of the right channel.
OUTPR	18	O	Class-D H-bridge positive output for right channel.
PGND	19	P	Power ground for the H-bridges.
OUTNR	20	O	Class-D H-bridge negative output for right channel.
BSNR	21	P	Bootstrap supply (BST) for negative high-side FET of the right channel.
BSNL	22	P	Bootstrap supply (BST) for negative high-side FET of the left channel.
OUTNL	23	O	Class-D H-bridge negative output for left channel.
PGND	24	P	Power ground for the H-bridges.
Thermal Pad		P	Connect to GND for best thermal and electrical performance

(1)   I = Input, O = Output, IO = Input and Output, P = Power

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)[1]

		MIN	MAX	UNIT
Supply voltage	AVCC to GND, PVCC to GND	−0.3	20	V
Input current	To any pin except supply pins		10	mA
Slew rate, maximum[2]	$\overline{SD}/\overline{FAULT}$ to GND, GAIN_SEL, MODE_SEL, MUTE		10	V/ms
Interface pin voltage	$\overline{SD}/\overline{FAULT}$ to GND, GAIN_SEL, MODE_SEL, MUTE	−0.3	AVCC + 0.3	V
	PLIMIT	-0.3	GVDD + 0.3	V
	RINN, RINP, LINN, LINP	−0.3	5.5	V
Minimum load resistance, R_L	BTL, (10 V ≤ PVCC ≤ 14.4 V)	4.8		Ω
	BTL, (3.5 V < PVCC < 10 V)	3.2		
	PBTL, (10 V ≤ PVCC < 14.4 V)	2.4		
	PBTL, (3.5 V ≤ PVCC < 10 V)	1.6		
Continuous total power dissipation		See the Thermal Information Table		
Operating Junction Temperature range		−25	150	°C
Storage temperature range, T_{stg}		−40	125	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) The voltage slew rate of these pins must be restricted to no more than 10 V/ms. For higher slew rates, use a 100 kΩ resister in series with the pins.

6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 [1]	±1000	V
		Charged device model (CDM), per JEDEC specification JESD22-C101 [2]	±250	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

Over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	MAX	UNIT
V_{CC}	Supply voltage	PVCC, AVCC	3.5	14.4	V
V_{IH}	High-level input voltage	$\overline{SD}/\overline{FAULT}$ [1], MUTE, GAIN_SEL, MODE_SEL	2	AVCC	V
V_{IL}	Low-level input voltage	$\overline{SD}/\overline{FAULT}$, MUTE, GAIN_SEL, MODE_SEL[2]		0.8	V
V_{OL}	Low-level output voltage	$\overline{SD}/\overline{FAULT}$, $R_{PULL-UP}$ =100 kΩ, PVCC = 14.4 V		0.8	V
I_{IH}	High-level input current	$\overline{SD}/\overline{FAULT}$, MUTE, GAIN_SEL, MODE_SEL, V_I = 2 V, AVCC = 12 V		50	µA
I_{IL}	Low-level input current	$\overline{SD}/\overline{FAULT}$, MUTE, GAIN_SEL, MODE_SEL, V_I = 0.8 V, AVCC = 12 V		5	µA
T_A	Operating free-air temperature[3] [4]		−10	85	°C
T_J	Operating junction temperature[3]		-10	150	°C

(1) Set $\overline{SD}/\overline{FAULT}$ to high level, make sure the pull-up resistor is larger than 4.7 kΩ and smaller than 500 kΩ
(2) Set GAIN_SEL and MODE_SEL to low level, make sure pull down resistor<10 kΩ
(3) The TPA3138D2 incorporates an exposed thermal pad on the underside of the chip. This acts as a heatsink, and it must be connected to a thermally dissipating plane for proper power dissipation. Failure to do so may result in the device going into thermal protection shutdown. See TI Technical Briefs SLMA002 for more information about using the TSSOP thermal pad.
(4) TPA3139D2 supports -40°C ~85°C ambient temperature range with ≤12 V operating PVDD range.

6.4 Thermal Information

THERMAL METRIC[1]		TPA3139D2	UNIT
		RGE (QFN)	
		24 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	37.4	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	35.1	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	16.8	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	0.9	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	16.7	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	7.3	°C/W

(1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, SPRA953.

6.5 Electrical Characteristics

T_A = 25°C, AVCC = PVCC = 12 V, RL = 8 Ω, Gain = 20 dB, ferrite beads used, unless otherwise noted.

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
AC CHARACTERISTICS						
P_O	Output power (BTL), 10% THD+N	PV_{CC} = 7.4 V, R_L = 8 Ω, f = 1 kHz, 1SPW mode		3.8		W
		PV_{CC} = 12 V, R_L = 4 Ω, f = 1 kHz, BD mode		14.3		W
	Output power (BTL), 1% THD+N	PV_{CC} = 7.4 V, R_L = 8 Ω, f = 1 kHz, 1SPW mode		3.0		W
		PV_{CC} = 12 V, R_L = 4 Ω, f = 1 kHz, BD mode		13.6		W
	Output power (PBTL), 10% THD+N	PV_{CC} = 5 V, R_L = 4 Ω, f = 1 kHz, 1SPW mode		3.5		W
		PV_{CC} = 12 V, R_L = 4 Ω, f = 1 kHz, BD mode		19.1		
		PV_{CC} = 12 V, R_L = 8 Ω, f = 1 kHz, BD mode		10.5		W
	Output power (PBTL), 1% THD+N	PV_{CC} = 5 V, R_L = 4 Ω, f = 1 kHz, 1SPW mode		3		W
		PV_{CC} = 12 V, R_L = 4 Ω, f = 1 kHz, BD mode		15.7		
		PV_{CC} = 12 V, R_L = 8 Ω, f = 1 kHz, BD mode		8.9		W
I_O	Maximum output current	f = 1 kHz, R_L = 3 Ω		3.5		A
THD+N	Total harmonic distortion + noise	f = 1 kHz, P_O = 5 W (half-power)		0.04		%
PSRR	Power supply ripple rejection	200-mV_{PP} ripple at 1 kHz, inputs ac-coupled to GND		-85		dB
V_n	Output integrated noise	20 Hz to 22 kHz, A-weighted filter, Gain = 26 dB		85		μV
				-81		dBV
		20 Hz to 22 kHz, A-weighted filter, Gain = 20 dB		72		μV
				-82.6		dBV
	Crosstalk	V_O = 1 Vrms, f = 1 kHz		-100		dB
SNR	Signal-to-noise ratio	Maximum output at THD+N < 1%, f = 1 kHz, A-weighted		102		dB
OTE	Thermal trip point			150		°C
	Thermal hysteresis			15		°C
DC CHARACTERISTICS						
| V_{OS} |	Output offset voltage (measured differentially)	V_I = 0 V		1.5		mV
I_{CC}	Quiescent supply current	$\overline{SD}$/ $\overline{FAULT}$ = 2 V, ferrite bead filter, 1SPW Mode, PV_{CC} = 12 V		20		mA
		$\overline{SD}$/ $\overline{FAULT}$ = 2 V, ferrite bead filter, BD Mode, PV_{CC} = 12 V		37		mA
		$\overline{SD}$/ $\overline{FAULT}$ = 2 V, 10 μH + 680 nF output filter, 1SPW Mode, PV_{CC} = 7.4 V		17		mA
		$\overline{SD}$/ $\overline{FAULT}$ = 2 V, 10 μH + 680 nF output filter, 1SPW Mode, PV_{CC} = 12 V		22.8		mA
$I_{CC(SD)}$	Quiescent supply current in shutdown mode	$\overline{SD}$/ $\overline{FAULT}$ = 0.8 V, no load		10		μA
$r_{DS(on)}$	Drain-source on-state resistance	I_O = 500 mA, T_J = 25°C excluding metal and bond wire resistance — High Side		180		mΩ
		I_O = 500 mA, T_J = 25°C excluding metal and bond wire resistance — Low side		180		
G	Gain	GAIN_SEL= 0.8 V	19	20	21	dB
		GAIN_SEL= 2 V	25	26	27	dB
t_{ON}	Turn-on time	$\overline{SD}$/ $\overline{FAULT}$ = 2 V		15		ms
t_{OFF}	Turn-off time	$\overline{SD}$/ $\overline{FAULT}$ = 0.8 V		2.9		μs
GVDD	Gate drive supply	I_{GVDD} = 2 mA	4.8	5	5.2	V
t_{DCDET}	DC detect time	V_{RINP} = 2.6 V and V_{RINN} = 2.4 V, or V_{RINP} = 2.4 V and V_{RINN} = 2.6 V		800		ms
OVP	Over Voltage Protection			15.8		V
UVP	Under Voltage Protection	MODE_SEL = 0.8 V (BD mode)		7.5		V
UVP	Under Voltage Protection	MODE_SEL = 2 V, or floating (1SPW mode)		3.4		V

Product Folder Links: *TPA3139D2*

6.6 Switching Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER		MIN	NOM	MAX	UNIT
$f_{OSC, SS}$	Oscillator frequency, Spread Spectrum ON	305		340	kHz

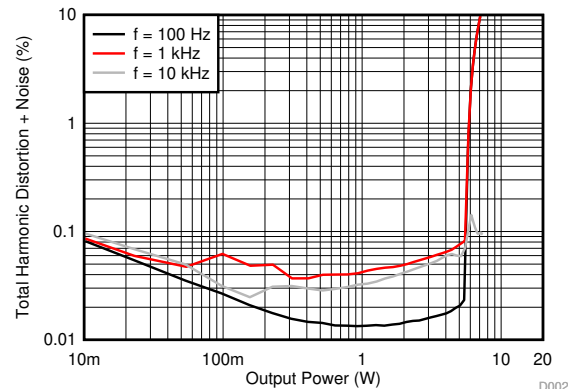Product Folder Links: *TPA3139D2*

6.7 Typical Characteristics,

6.7.1 Bridge -Tied Load (BTL)

All measurements taken at audio frequency = 1 kHz, closed-loop gain = 26 dB, BD Modulation, 10 µH + 0.68 µF, T_A = 25°C, AES17 measurement filter, unless otherwise noted.
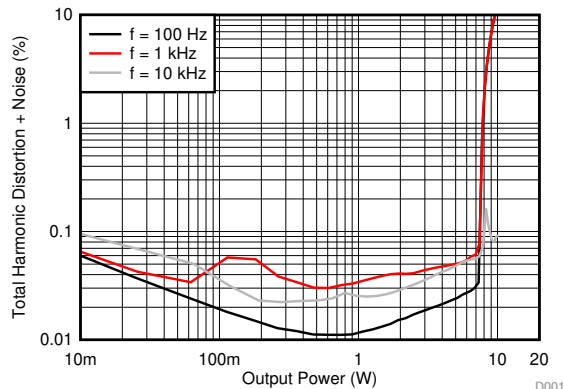
AVCC = PVCC = 12 V, Load = 8 Ω, LC Filter

図 6-1. THD+N vs Power (BTL)

AVCC=PVCC=8 V, Load = 4 Ω, LC Filter

図 6-2. THD+N vs Power (BTL)
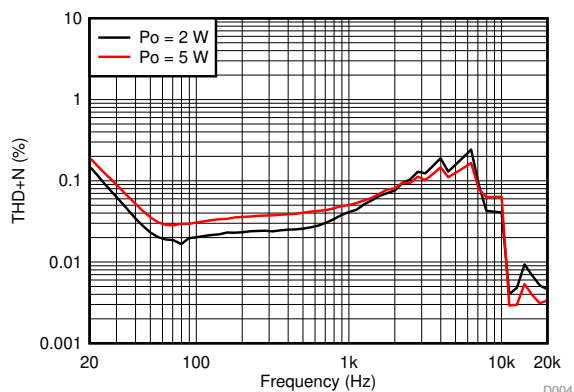
AVCC = PVCC = 12 V, Load = 8 Ω, LC Filter

図 6-3. THD+N vs Frequency (BTL)
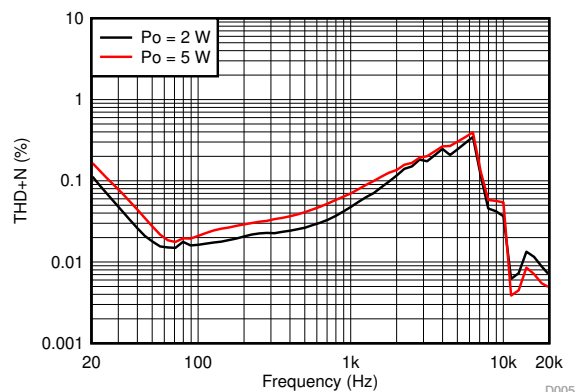
AVCC=PVCC=12 V, Load = 4 Ω

図 6-4. THD+N vs Frequency (BTL)
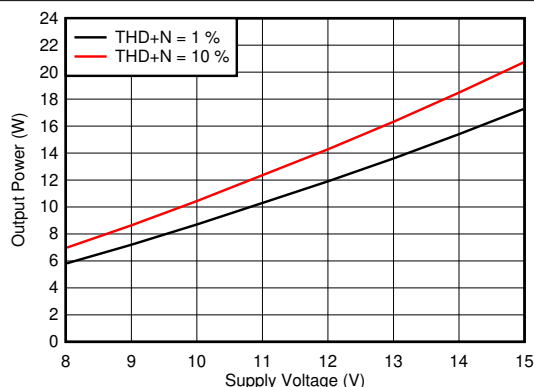
Load = 4 Ω

図 6-5. Output Power vs Supply Voltage (BTL)

Load = 8 Ω

図 6-6. Output Power vs Supply Voltage (BTL)

Product Folder Links: TPA3139D2
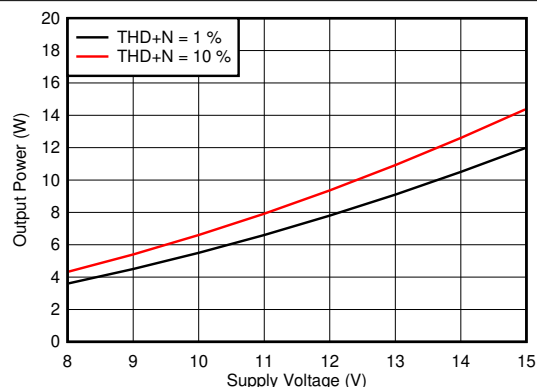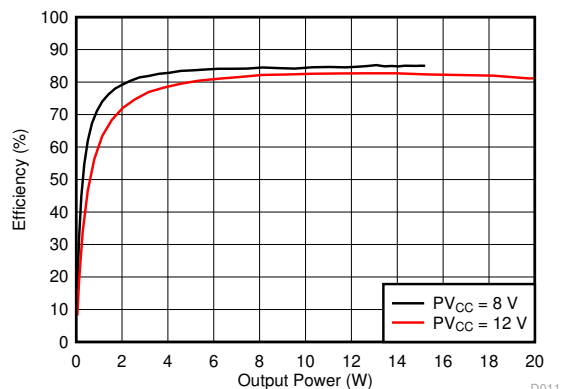
Load = 4 Ω

図 6-7. Efficiency vs Output Power (BTL)
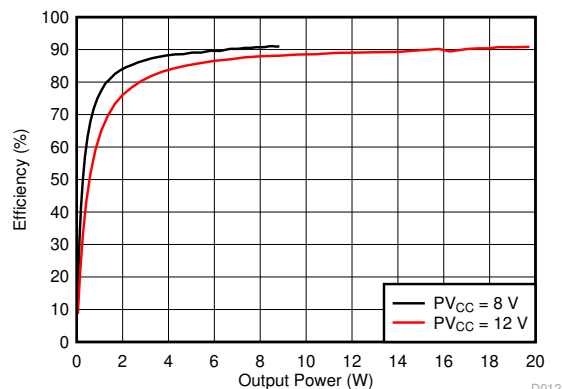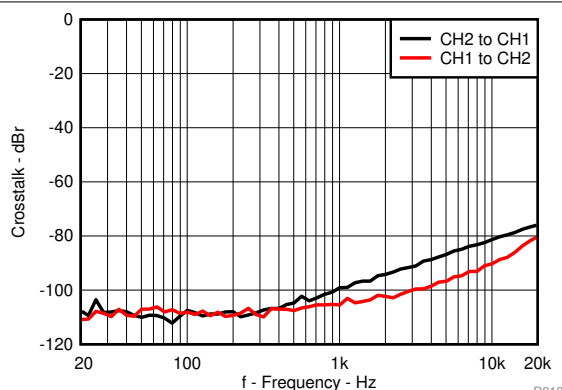
A. Load = 8 Ω

図 6-8. Efficiency vs Output Power (BTL)
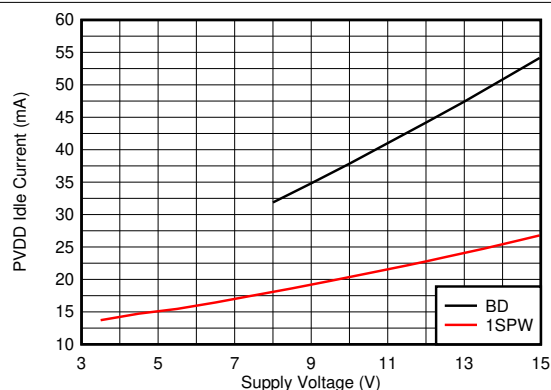
Load = 8 Ω, 1SPW and BD
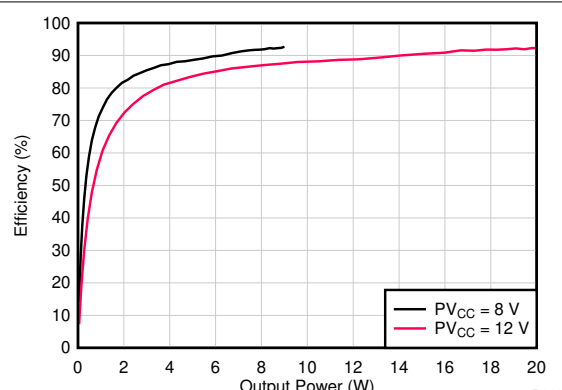
図 6-9. Idle Power vs Supply Voltage (BTL)
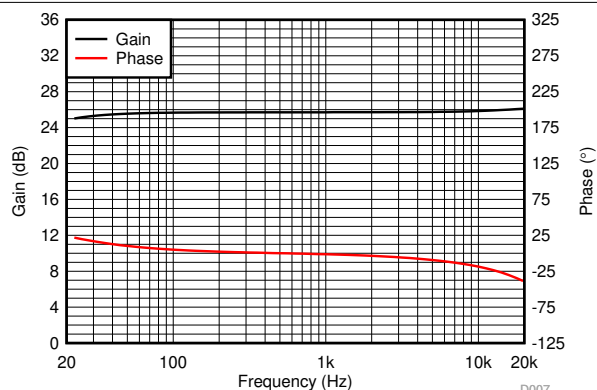
A. AVCC= PVCC = 12 V   Load = 6 Ω + 47 µH
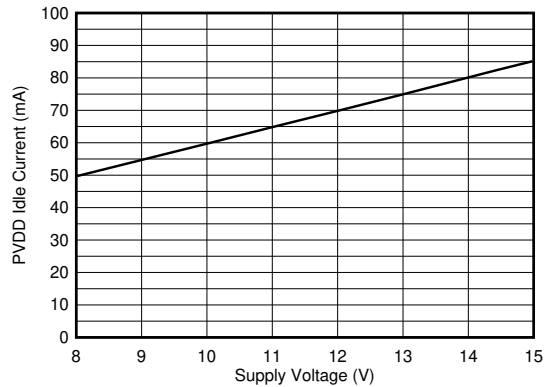
図 6-10. Gain and Phase vs Frequency (BTL)

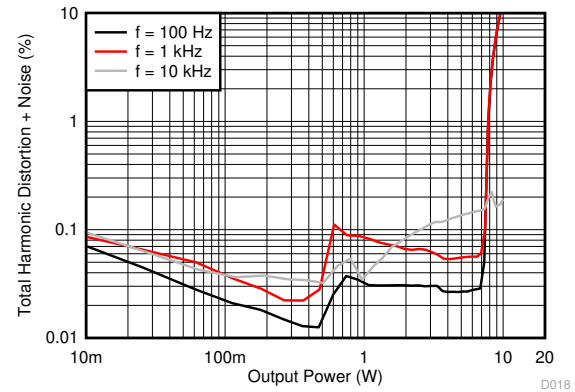AVCC=PVCC = 12 V, 1 W   Load = 6 Ω + 47 µH

図 6-11. Crosstalk vs Frequency (BTL)

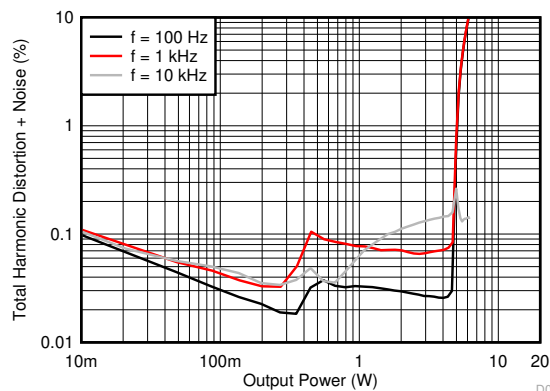A.   Load = 8 Ω   Ferrite Bead Filter

図 6-12. Efficiency vs Output Power, 8 Ω
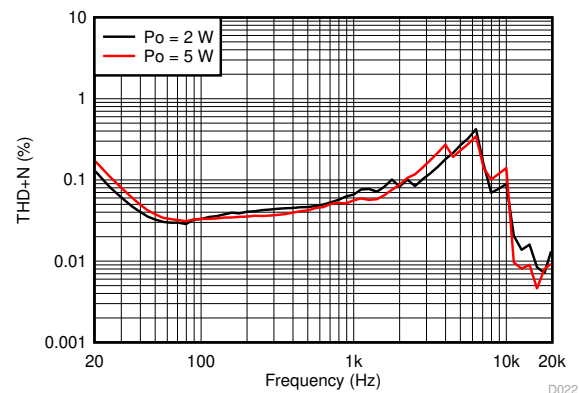
Product Folder Links: *TPA3139D2*

A.　　　　Load = 8 Ω　　Ferrite Bead Filter

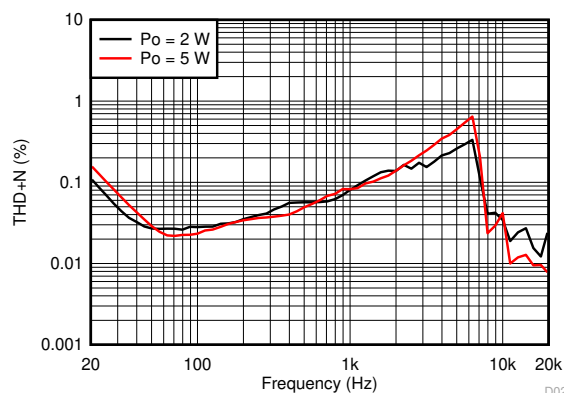**図 6-13. Idle Current vs Supply Voltage, 8 Ω**

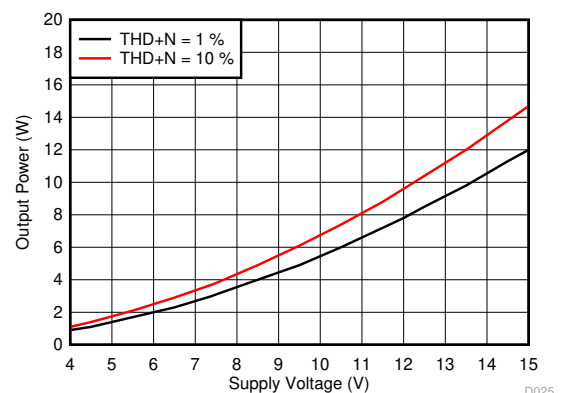A.　　AVCC=PVCC = 12 V, 1 W　　Load = 8 Ω　　1SPW

図 6-14. THD+N vs Output Power, 8 Ω

A.　　AVCC=PVCC = 7.4 V　　Load = 4 Ω　　1SPW

図 6-15. THD+N vs Output Power, 4 Ω
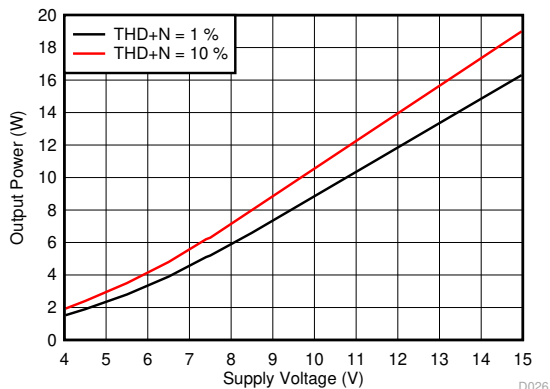

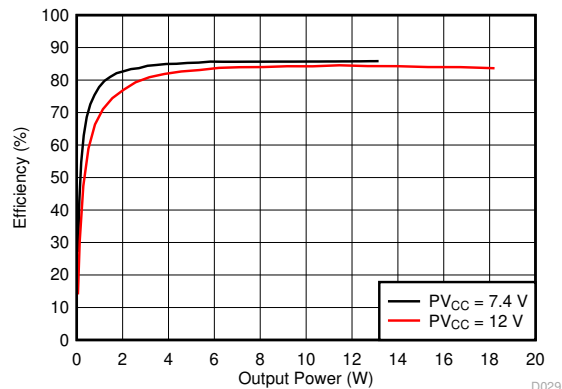A.　　AVCC=PVCC = 12 V　　Load = 8 Ω　　1SPW

図 6-16. THD+N vs Frequency, 8 Ω

A.　　AVCC=PVCC = 12 V　　Load = 4 Ω　　1SPW

図 6-17. THD+N vs Frequency, 4 Ω

A.　　Load = 8 Ω, 1SPW

図 6-18. Output Power vs Supply Voltage, 8 Ω

Product Folder Links: *TPA3139D2*

A.   Load = 4 Ω , 1SPW

図 6-19. Output Power vs Supply Voltage, 4 Ω

A.   Load = 4 Ω, 1SPW

図 6-20. Efficiency vs Output Power, 4 Ω

A.   Load = 8 Ω , 1SPW

図 6-21. Efficiency vs Output Power, 8 Ω

A.   Load = 8 Ω,   Ferrite Bead Filte   1SPW

図 6-22. Output Power vs Supply Voltage, 8 Ω

A.   Load = 8 Ω   Ferrite Bead Filter   1SPW

図 6-23. Idle Current vs Supply Voltage

Product Folder Links: *TPA3139D2*
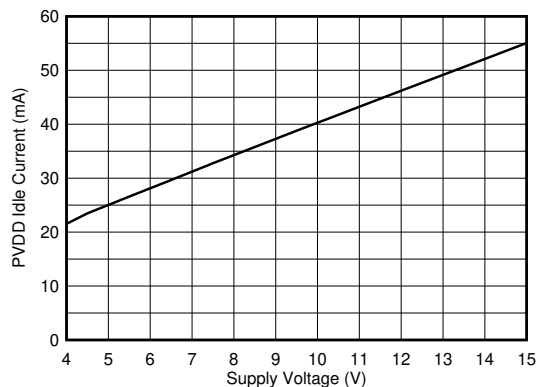
6.7.2 Paralleled Bridge -Tied Load (PBTL)

All measurements taken at audio frequency = 1 kHz, closed-loop gain = 20 dB, BD Modulation, 10 µH + 0.68 µF, T$_A$ = 25°C, AES17 measurement filter, unless otherwise noted.
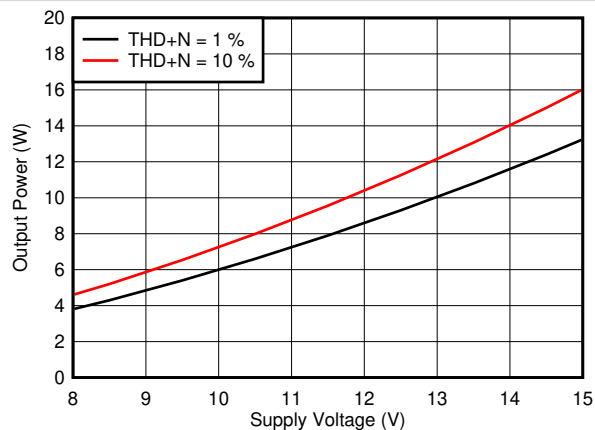
A. Load = 8 Ω

図 6-24. Output Power vs Supply Voltage, 8 Ω
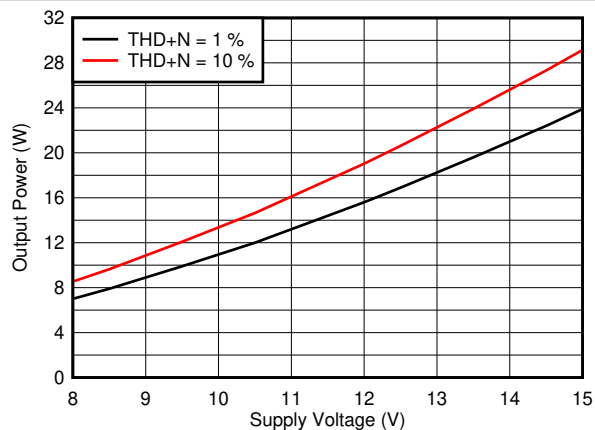
A. Load = 4 Ω

図 6-25. Output Power vs Supply Voltage, 4 Ω
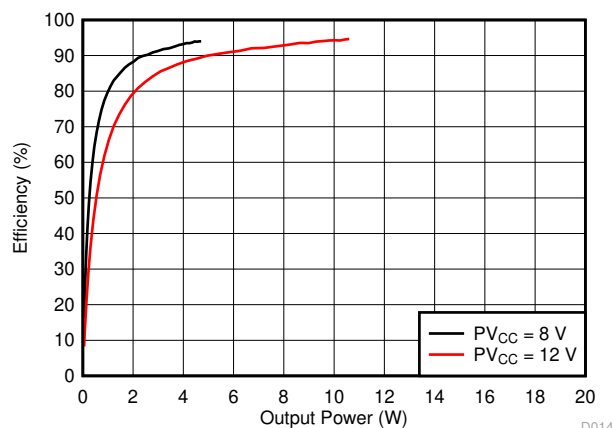
A. Load = 8 Ω

図 6-26. Efficiency vs Output Power, 8 Ω
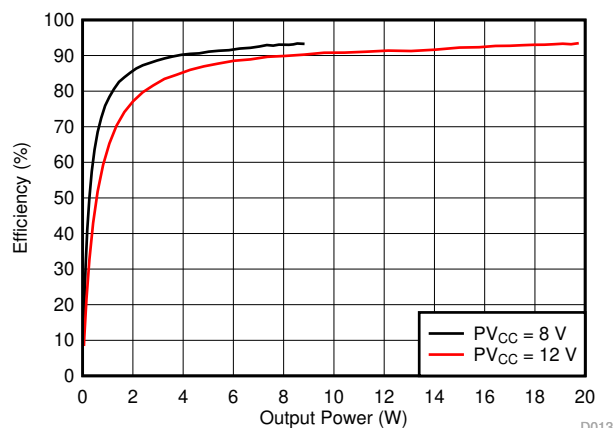
A. Load = 4 Ω

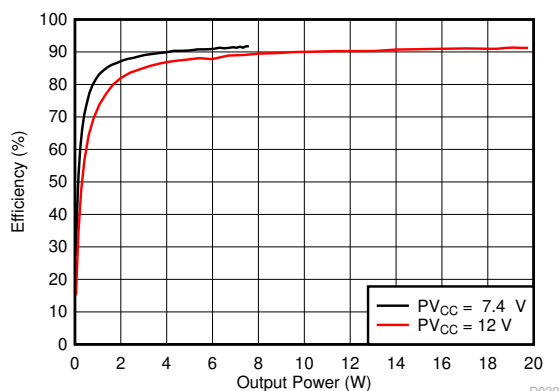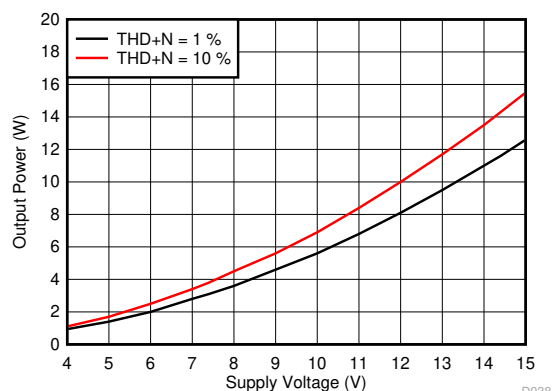**図 6-27. Efficiency vs Output Power, 4 Ω**

A. Load = 8 Ω, 1SPW
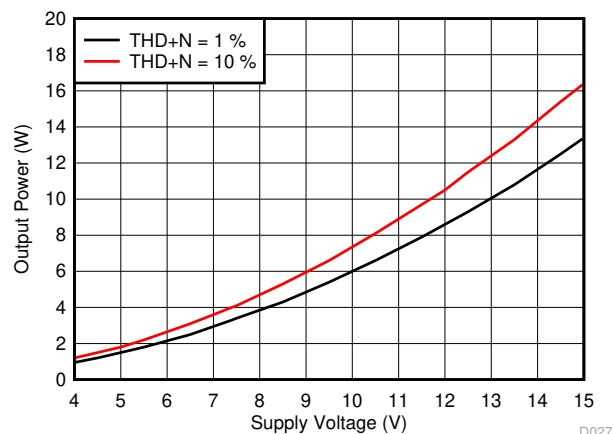
図 6-28. Output Power vs Supply Voltage, 8 Ω

A. Load = 4 Ω, 1SPW
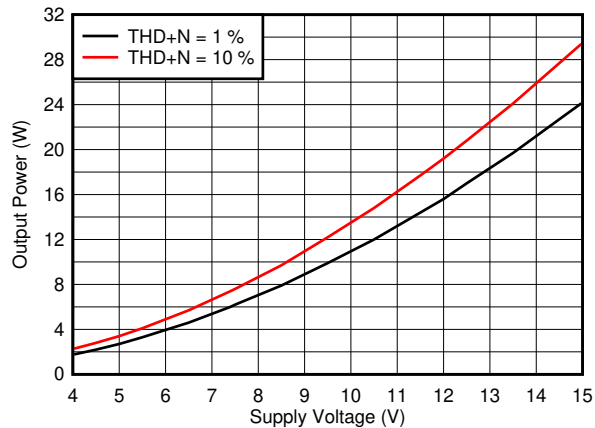
図 6-29. Output Power vs Supply Voltage, 4 Ω
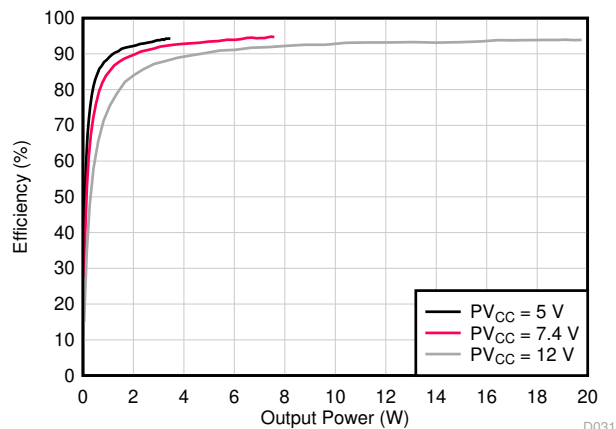
Product Folder Links: *TPA3139D2*

図 6-30. Efficiency vs Output Power, 8 Ω

A. Load = 8 Ω, 1SPW

図 6-31. Efficiency vs Output Power, 4 Ω

A. Load = 4 Ω, 1SPW

図 6-32. Output Power vs Supply, 4 Ω

A. Load = 4 Ω, Ferrite Bead Filter, 1SPW

Product Folder Links: *TPA3139D2*
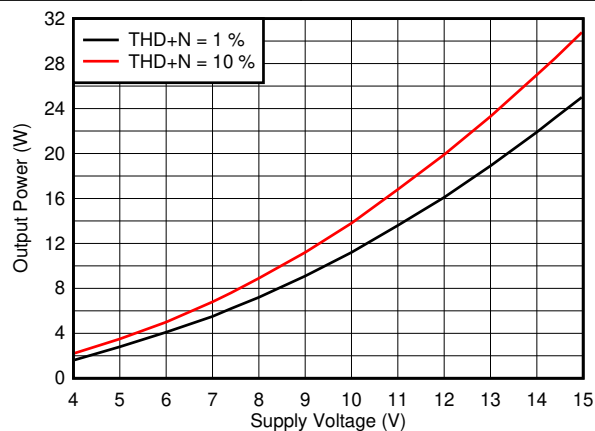
7 Detailed Description

7.1 Overview

The TPA3139D2 is designed as a low-idle-power, cost-effective, general-purpose Class-D audio amplifier. The fast turn-on time (15-ms) along with MUTE function allows TPA3139D2 to quickly power up while avoiding pop. The built-in spread spectrum control scheme efficiently suppresses EMI and enables the use of ferrite beads instead of inductors for ≤ 2 x 10 W applications.

To facilitate system design, the TPA3139D2 needs only one power supply between 3.5 V and 14.4 V for operation. An internal voltage regulator provides suitable voltage levels for the gate driver, digital, and low-voltage analog circuitry. For a properly functioning bootstrap circuit, a small ceramic capacitor must be connected from each bootstrap pin (BSxx) to the power-stage output pin (OUTxx). When the power-stage output is low, the bootstrap capacitor is charged through an internal diode connected between the gate-drive power-supply pin (GVDD) and the bootstrap pins. When the power-stage output is high, the bootstrap capacitor potential is shifted above the output potential and thus provides a suitable voltage supply for the high-side gate driver. In an application with PWM switching frequencies in the datasheet specified range, use ceramic capacitors with at least 220-nF capacitance, size 0603 or 0805, for the bootstrap supply. These capacitors ensure sufficient energy storage, even during clipped low frequency audio signals, to keep the high-side power stage FET (LDMOS) fully turned on during the remaining part of its ON cycle.

The audio signal path, including the gate drive and output stage, is designed as identical, independent full-bridges. All decoupling capacitors should be placed as close as possible to their associated pins. The physical loop with the power supply pins, decoupling capacitors, and GND return path to the device pins must be kept as short as possible, and with as little area as possible to minimize induction.

Special attention should be paid to the power-stage power supply; this includes component selection, PCB placement, and routing. For optimal electrical performance, EMI compliance, and system reliability, each PVCC pin should be decoupled with ceramic capacitors that are placed as close as possible to each supply pin. It is recommended to follow the PCB layout of the TPA3139D2 reference design. For additional information on recommended power supply and required components, see the application diagrams in this data sheet.

The PVCC power supply should have low output impedance and low noise. The power-supply ramp and $\overline{SD}$/$\overline{FAULT}$ release sequence is not critical for device reliability as facilitated by the internal power-on-reset circuit, but it is recommended to release $\overline{SD}$/ $\overline{FAULT}$ after the power supply is settled for minimum turn-on audible artifacts.

7.2 Functional Block Diagram

Product Folder Links: *TPA3139D2*
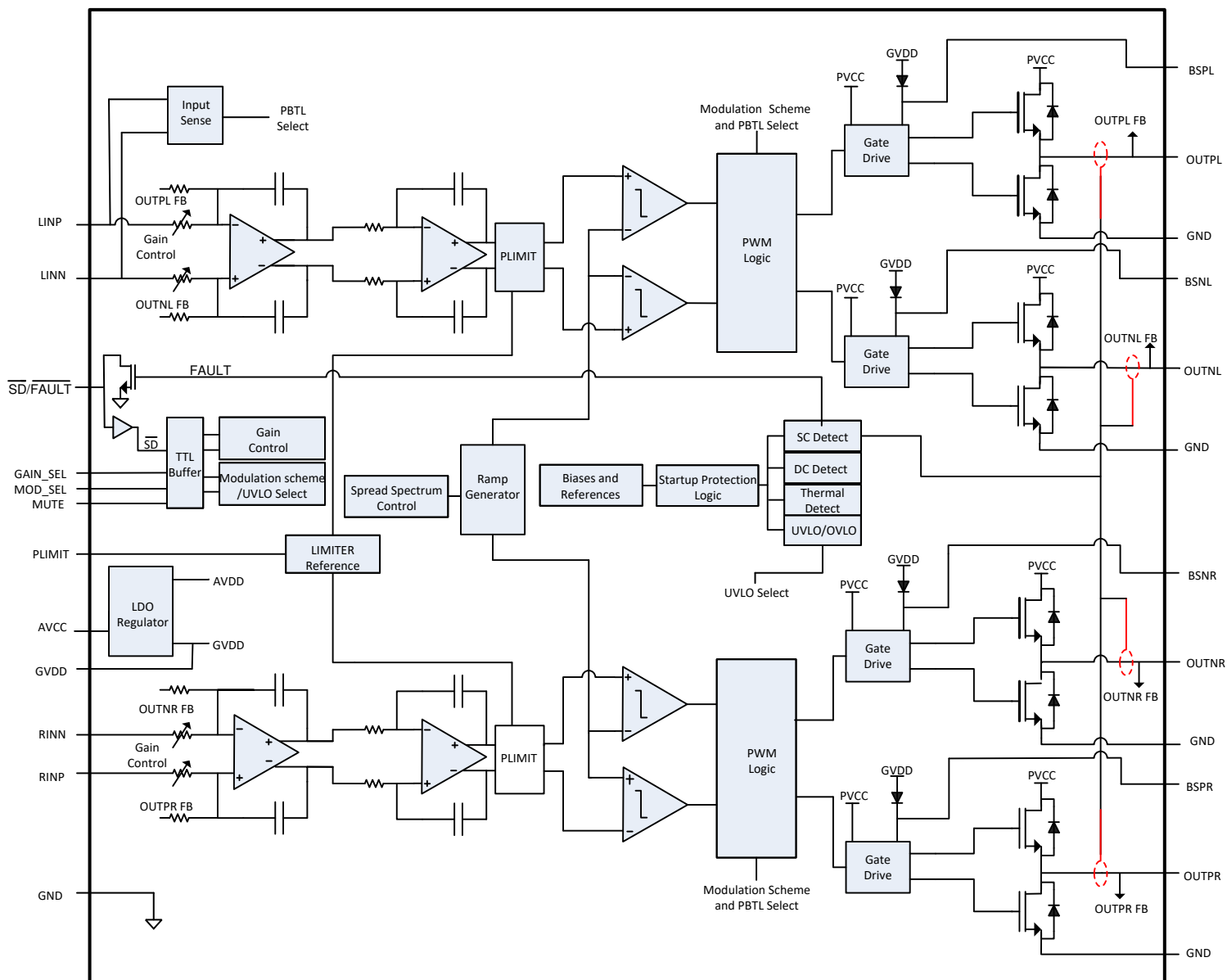
7.3 Feature Description

7.3.1 Analog Gain

The analog gain of the TPA3139D2 can be changed by GAIN_SEL pin. Low Level, Gain = 20 dB; High Level, Gain = 26 dB.

7.3.2 $\overline{SD}$/ $\overline{FAULT}$ and MUTE Operation

The TPA3139D2 device employs a shutdown mode of operation designed to reduce supply current (I_{CC}) to the absolute minimum level during periods of nonuse for power conservation. The $\overline{SD}$/ $\overline{FAULT}$ input pin should be held high (see セクション 6 table for trip point) during normal operation when the amplifier is in use. Pulling $\overline{SD}$/ $\overline{FAULT}$ low causes the outputs to mute and the amplifier to enter a low-current state. Never leave $\overline{SD}$/ $\overline{FAULT}$ unconnected, because the amplifier operation would be unpredictable.

For the best power-off pop performance, place the amplifier in the shutdown or mute mode prior to removing the power supply voltage.

For some single ended input application case, suggest to mute the device first then release $\overline{SD}$/ $\overline{FAULT}$, then umute the output. This sequence power-up sequence with best pop performance.

7.3.3 PLIMIT

If selected, the PLIMIT operation limits the output voltage to a level below the supply rail. If the amplifier operates like it is powered by a lower supply voltage, then it limits the output power by voltage clipping. Add a resistor divider from GVDD to ground to set the threshold voltage at the PLIMIT pin.
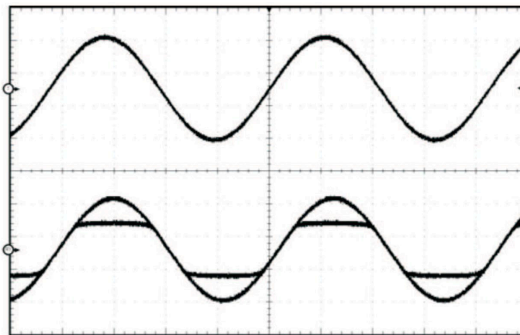
図 7-1. PLIMIT Circuit Operation

The PLIMIT circuit sets a limit on the output peak-to-peak voltage. The limiting is done by limiting the duty cycle to a fixed maximum value. The limit can be thought of as a "virtual" voltage rail which is lower than the supply connected to PVCC. The "virtual" rail is approximately 5.7 times (with BD mode) and 11.4 times (with 1SPW mode) the voltage at the PLIMIT pin. The output voltage can be used to calculate the maximum output power for a given maximum input voltage and speaker impedance.

$$P_{OUT} = \frac{\left(\left(\frac{R_L}{R_L + 2 \times R_S}\right) \times V_P\right)^2}{2 \times R_L} \quad \text{for unclipped power}$$

(1)

where

- P_{OUT} (10%THD) = 1.25 × P_{OUT} (unclipped)
- R_L is the load resistance.
- R_S is the total series resistance including $R_{DS(on)}$, and output filter resistance.
- V_P is the peak amplitude, which is limited by "virtual" voltage rail.

7.3.4 Spread Spectrum and De-Phase Control

The TPA3139D2 device has built-in spread spectrum control of the oscillator frequency and de-phase of the PWM outputs to improve EMI performance. The spread spectrum scheme is internally fixed and is always turned on.

De-phase inverts the phase of the output PWM such that the idle output PWM waveforms of the two audio channels are inverted. De-phase does not affect the audio signal, or its polarity. De-phase only works with BD mode, it is auto-disabled in 1SPW mode.

7.3.5 GVDD Supply

The GVDD Supply is used to power the gates of the output full-bridge transistors. Add a 1-µF capacitor to ground at this pin.

7.3.6 DC Detect

The TPA3139D2 device integrates a circuitry which protects the speakers from DC current that might occur due to defective capacitors on the input or shorts on the printed circuit board at the inputs. A DC detect fault is reported on the $\overline{SD}/\overline{FAULT}$ pin as a low state. The DC Detect fault also causes the amplifier to shutdown by changing the state of the outputs to Hi-Z.

A DC Detect Fault is issued when the output DC voltage sustain for more than 800 msec at the same polarity. This feature protects the speaker from large DC currents or AC currents less than 1 Hz. To avoid nuisance faults due to the DC detect circuit, hold the $\overline{SD}/\overline{FAULT}$ pin low at power-up until the signals at the inputs are stable. Also, take care to match the impedance seen at the positive and negative inputs to avoid nuisance DC detect faults.

7.3.7 PBTL Select

The TPA3139D2 device offers the feature of Parallel BTL operation with two outputs of each channel connected directly. Connecting LINP and LINN directly to Ground (without capacitors) sets the device in Mono Mode during power up. Connect the OUTPR and OUTNR together for the positive speaker terminal and OUTNL and OUTPL together for the negative speaker terminal. Analog input signal is applied to INPR and INNR. For an example of the PBTL connection, see the schematic in the *セクション 8.2* section.

7.3.8 Short-Circuit Protection and Automatic Recovery Feature

The TPA3139D2 features over-current conditions against the output stage short-circuit conditions. The short-circuit protection fault is reported on the $\overline{SD}/\overline{FAULT}$ pin as a low state. The amplifier outputs are switched to a Hi-Z state when the short circuit protection latch is triggered .

The device recovers automatically once the over-current condition has been removed.

7.3.9 Over-Temperature Protection (OTP)

Thermal protection on the TPA3139D2 device prevents damage to the device when the internal die temperature exceeds 150°C. This triggering point has a ±15°C tolerance from device to device. Once the die temperature exceeds the thermal triggering point, the device is switched to the shutdown state and the outputs are disabled.

Thermal protection faults are reported on the $\overline{SD}/\overline{FAULT}$ pin.

Product Folder Links: *TPA3139D2*

The device recovers automatically once the over temperature condition has been removed.

7.3.10 Over-Voltage Protection (OVP)

The TPA3139D2 device monitors the voltage on PVCC voltage threshold. When the voltage on PVCCL pin and PVCCR pin exceeds the over-voltage threshold (15.8 V typ), the OVP circuit puts the device into shutdown mode.

The device recovers automatically once the over-voltage condition has been removed.

7.3.11 Under-Voltage Protection (UVP)

When the voltage on PVCCL pin and PVCCR pin falls below the under-voltage threshold, the UVP circuit puts the device into shutdown mode. When MODE_SEL pin is set to LOW (BD mode), the under-voltage threshold is 7.5 V typical. When MODE_SEL pin is set to HIGH or floating, the TPA3139D2 operates in 1SPW mode, and the under-voltage threshold is 3.4 V typical.

The device recovers automatically once the under-voltage condition has been removed.

7.4 Device Functional Modes

7.4.1 MODE_SEL = LOW: BD Modulation

This is a modulation scheme that allows operation without the classic LC reconstruction filter when the amp is driving an inductive load with short speaker wires. Each output is switching from 0 volts to the supply voltage. The OUTPx and OUTNx are in phase with each other with no input so that there is little or no current in the speaker. The duty cycle of OUTPx is greater than 50% and OUTNx is less than 50% for positive output voltages. The duty cycle of OUTPx is less than 50% and OUTNx is greater than 50% for negative output voltages. The voltage across the load sits at 0 V throughout most of the switching period, reducing the switching current, which reduces any I^{2}R losses in the load.

図 7-2. BD Mode Modulation

Product Folder Links: *TPA3139D2*
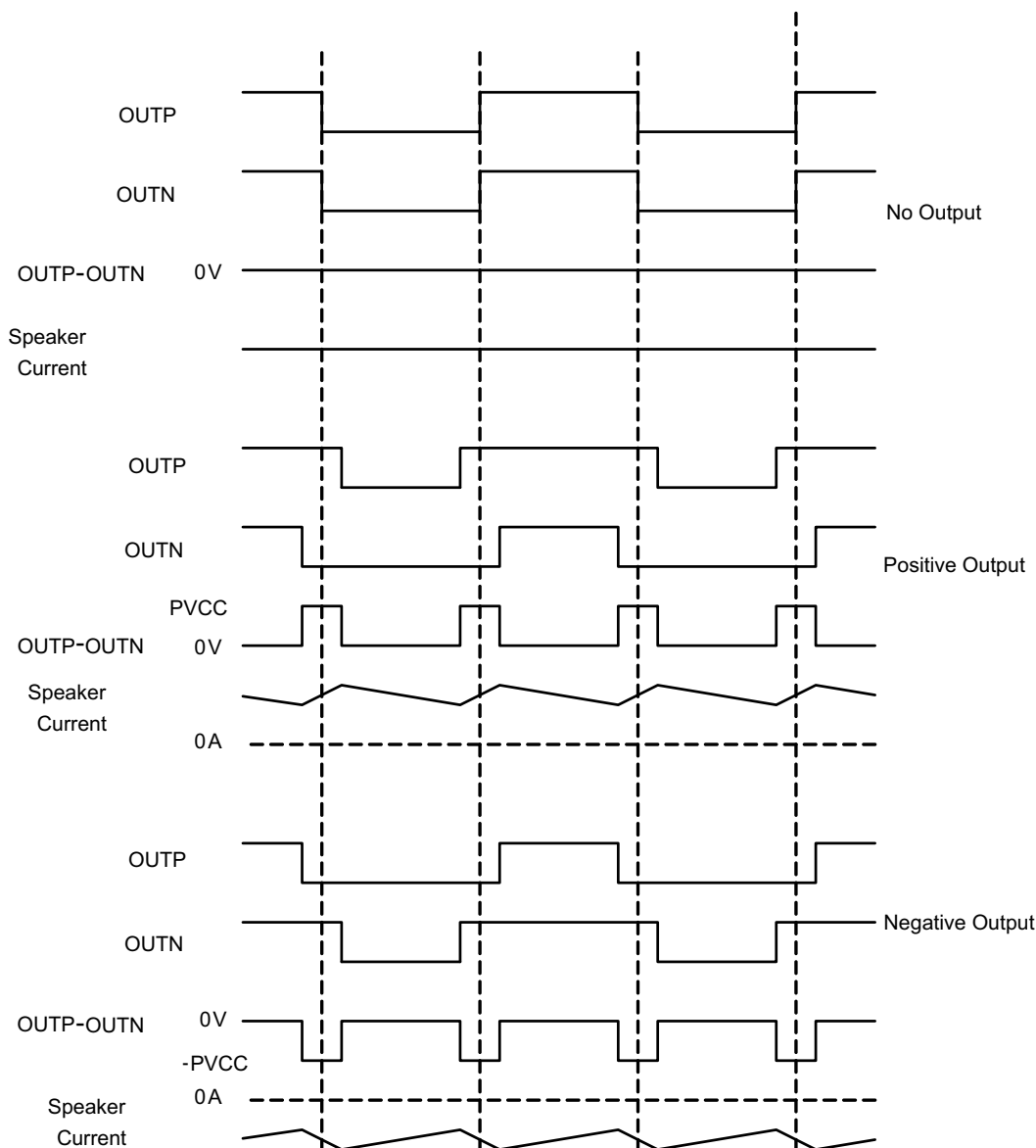
7.4.2 MODE_SEL = HIGH: Low-Idle-Current 1SPW Modulation

The 1SPW mode alters the normal modulation scheme in order to achieve higher efficiency with a slight penalty in THD degradation and more attention required in the output filter selection. In 1SPW mode, the outputs operate at ~15% modulation during idle conditions. When an audio signal is applied, one output decreases and the other output increases. The decreasing output signal rails to GND. At which point, all the audio modulation takes place through the rising output. The result is that only one output is switching during a majority of the audio cycle. Efficiency is improved in this mode due to the reduction of switching losses.
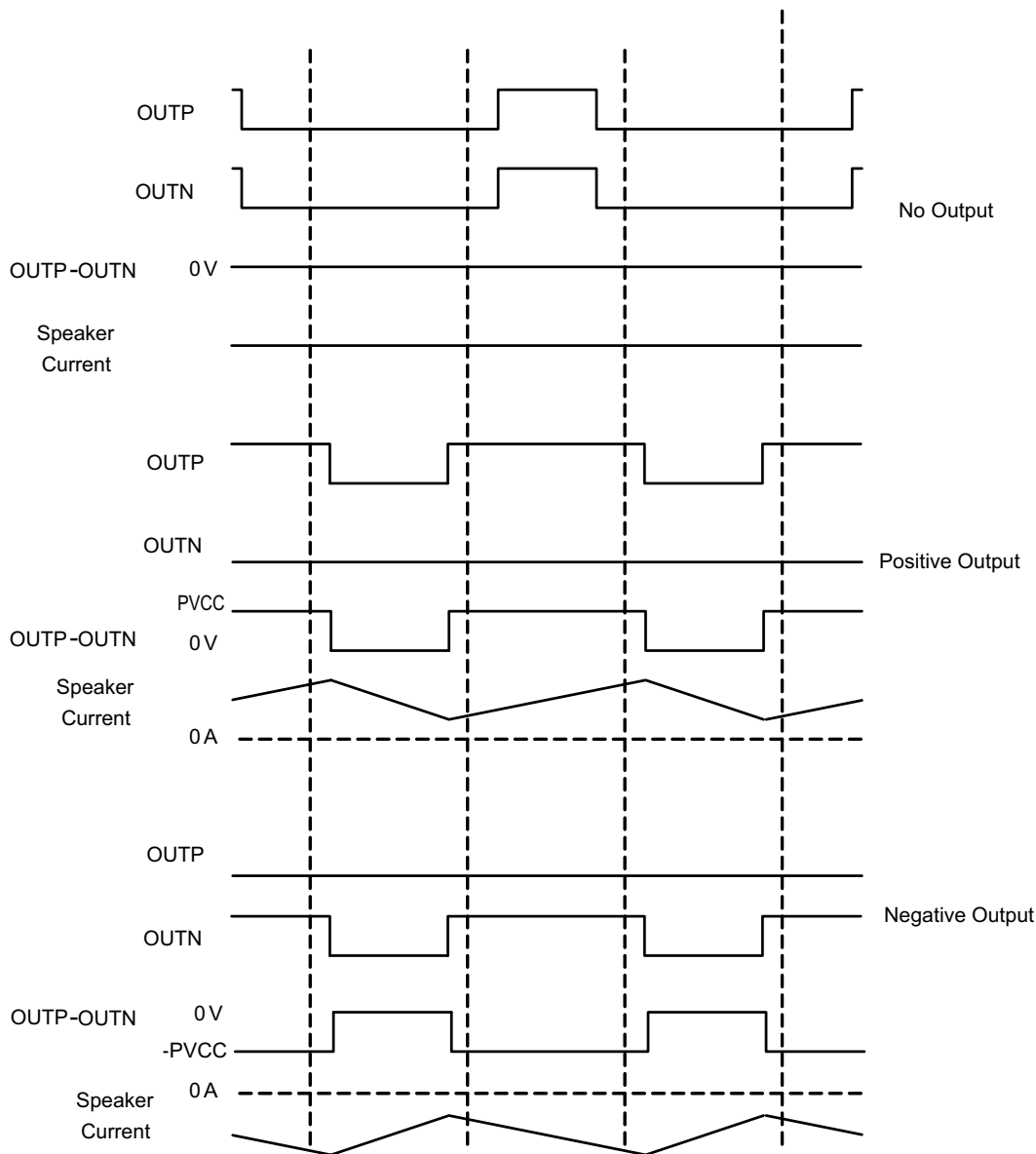
図 7-3. Low-Idle-Current 1SPW Modulation

8 Application and Implementation

Note

以下のアプリケーション情報は、TI の製品仕様に含まれるものではなく、TI ではその正確性または完全性を保証いたしません。個々の目的に対する製品の適合性については、お客様の責任で判断していただくことになります。お客様は自身の設計実装を検証しテストすることで、システムの機能を確認する必要があります。

8.1 Application Information

The TPA3139D2 device is designed for use in inductor-free applications with limited distance wire length between amplifier and speakers, suitable for applications such as TV sets, sound docks and Bluetooth speakers. The TPA3139D2 device can either be configured in stereo or mono mode. Depending on the output power requirements and necessity for (speaker) load protection, the built-in PLIMIT circuit can be used to control the system power, see functional description of these features.

8.2 Typical Applications
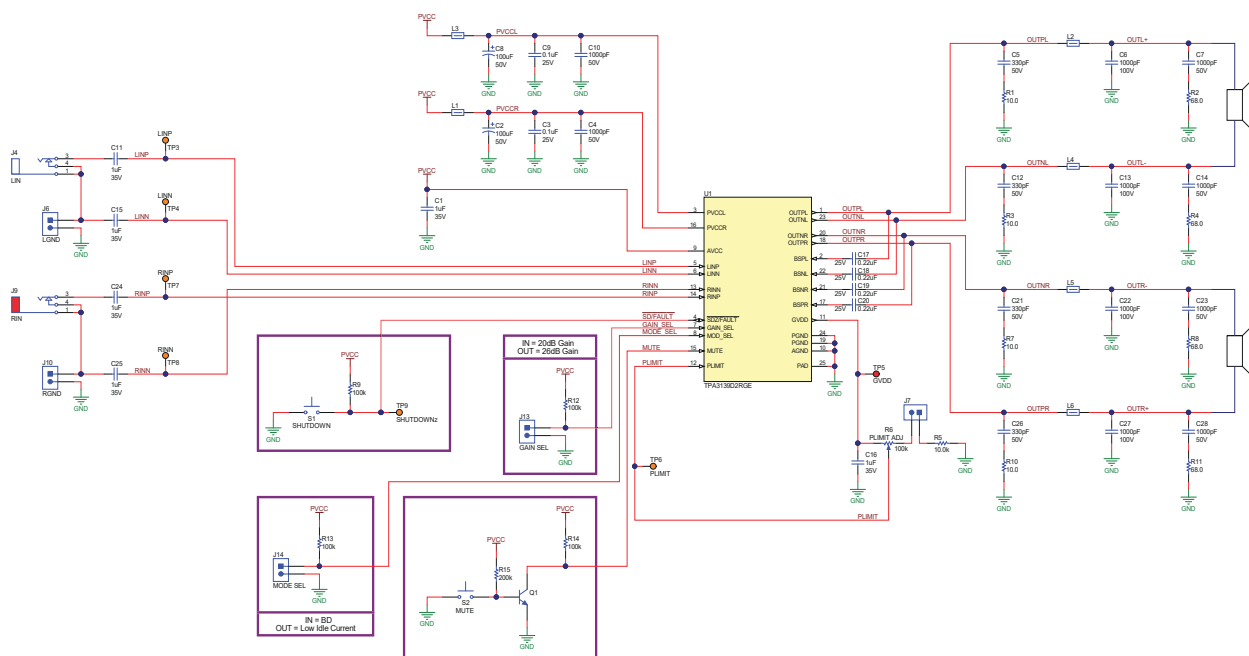
図 8-1. Stereo Class-D Amplifier in BTL Configuration with Single-Ended Inputs, Spread Spectrum Modulation and BD Mode
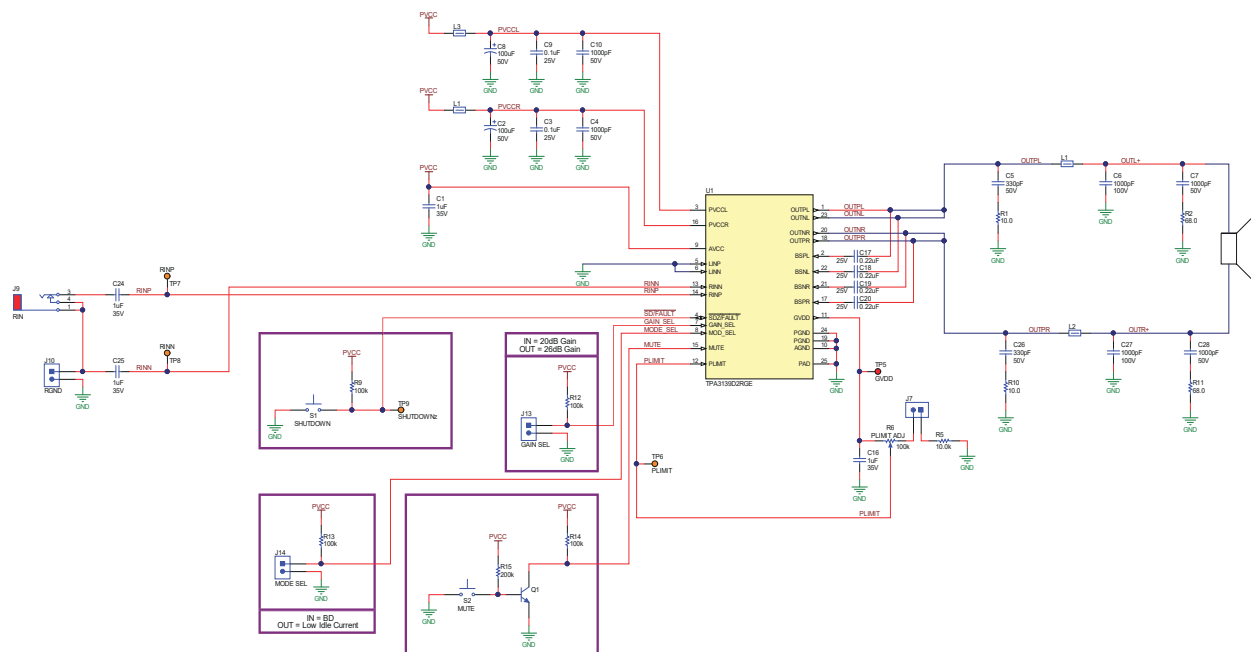
図 8-2. Stereo Class-D Amplifier in PBTL Configuration with Single-Ended Input, Spread Spectrum Modulation and 1SPW Mode

8.2.1 Design Requirements

8.2.1.1 PCB Material Recommendation

FR-4 Glass Epoxy material with 1 oz. (35 µm) is recommended for use with the TPA3139D2. The use of this material can provide higher power output, improved thermal performance, and better EMI margin (due to lower PCB trace inductance). It is recommended to use several GND underneath the device thermal pad for thermal coupling to a bottom-side copper GND plane for best thermal performance.

8.2.1.2 PVCC Capacitor Recommendation

The large capacitors used in conjunction with each full-bridge, are referred to as the PVCC capacitors. These capacitors should be selected for proper voltage margin and adequate capacitance to support the power requirements. In practice, with a well designed system power supply, a capacitor with 100 µF and 16 V supports most applications with 12-V power supply. 25-V capacitor rating is recommended for power supply voltage higher than 12 V. For The PVCC capacitors should be low ESR type because they are used in a circuit associated with high-speed switching.

Product Folder Links: *TPA3139D2*

8.2.1.3 Decoupling Capacitor Recommendations

In order to design an amplifier that has robust performance, passes regulatory requirements, and exhibits good audio performance, good quality decoupling capacitors should be used. In practice, X7R should be used in this application.

The voltage of the decoupling capacitors should be selected in accordance with good design practices. Temperature, ripple current, and voltage overshoot must be considered. This fact is particularly true in the selection of the ceramic capacitors that are placed on the power supply to each full-bridge. They must withstand the voltage overshoot of the PWM switching, the heat generated by the amplifier during high power output, and the ripple current created by high power output. A minimum voltage rating of 16 V is required for use with a 12-V power supply.

8.2.2 Detailed Design Procedure

A rising-edge transition on $\overline{SD}/\overline{FAULT}$ input allows the device to start switching. It is recommended to ramp the PVCC voltage to its desired value before releasing $\overline{SD}/\overline{FAULT}$ for minimum audible artifacts.

The device is not inverting the audio signal from input to output.

The GVDD pin is not recommended to be used as a voltage source for external circuitry.

8.2.2.1 Ferrite Bead Filter Considerations

With Advanced Emissions Suppression Technology, the TPA3139D2 amplifier delivers high-efficiency Class-D performance while minimizing interference to surrounding circuits, even with a low-cost ferrite bead filter. But couple factors need to be taken into considerations when selecting the ferrite beads.

One important aspect of the ferrite bead selection is the type of material used in the ferrite bead. Not all ferrite material is alike, so it is important to select a material that is effective in the 10 to 100 MHz range which is key to the operation of the Class-D amplifier. Many of the specifications regulating consumer electronics have emissions limits as low as 30 MHz. It is important to use the ferrite bead filter to block radiation in the 30-MHz and above range from appearing on the speaker wires and the power supply lines which are good antennas for these signals. The impedance of the ferrite bead can be used along with a small capacitor with a value in the range of 1000 pF to reduce the frequency spectrum of the signal to an acceptable level. For best performance, the resonant frequency of the ferrite bead and capacitor filter should be less than 10 MHz.

Also, it is important that the ferrite bead is large enough to maintain its impedance at the peak currents expected for the amplifier. Some ferrite bead manufacturers specify the bead impedance at a variety of current levels. If it is possible, make sure the ferrite bead maintains an adequate amount of impedance at the peak current that the amplifier detects. If these specifications are not available, it is possible to estimate the bead current handling capability by measuring the resonant frequency of the filter output at low power and at maximum power. A change of resonant frequency of less than fifty percent under this condition is desirable. Examples of ferrite beads which have been tested and work well with the TPA3139D2 device include NFZ2MSM series from Murata.

A high-quality ceramic capacitor is also required for the ferrite bead filter. A low ESR capacitor with good temperature and voltage characteristics works best.

Additional EMC improvements may be obtained by adding snubber networks from each of the class-D outputs to ground. Suggested values for a simple RC series snubber network would be 68 Ω in series with a 100-pF capacitor although design of the snubber network is specific to every application and must be designed taking into account the parasitic reactance of the printed circuit board as well as the audio amp. Take care to evaluate the stress on the component in the snubber network especially if the amp is running at high PVCC. Also, make sure the layout of the snubber network is tight and returns directly to the GND or the thermal pad beneath the chip.

8.2.2.2 Efficiency: LC Filter Required with the Traditional Class-D Modulation Scheme

The main reason that the traditional class-D amplifier requires an output filter is that the switching waveform results in maximum current flow. This causes more loss in the load, which causes lower efficiency. The ripple current is large for the traditional modulation scheme, because the ripple current is proportional to voltage multiplied by the time at that voltage. The differential voltage swing is $2 \times V_{CC}$, and the time at each voltage is half the period for the traditional modulation scheme. An ideal LC filter is required to store the ripple current from each half cycle for the next half cycle, while any resistance causes power dissipation. The speaker is both resistive and reactive, whereas an LC filter is almost purely reactive.

The TPA3139D2 modulation scheme has little loss in the load without a filter because the pulses are short and the change in voltage is V_{CC} instead of $2 \times V_{CC}$. As the output power increases, the pulses widen, making the ripple current larger. Ripple current could be filtered with an LC filter for increased efficiency, but for most applications the filter is not required.

An LC filter with a cutoff frequency less than the class-D switching frequency allows the switching current to flow through the filter instead of the load. The filter has less resistance but higher impedance at the switching frequency than the speaker, which results in less power dissipation, therefore increasing efficiency.

8.2.2.3 When to Use an Output Filter for EMI Suppression

The TPA3139D2 device has been tested with a simple ferrite bead filter for a variety of applications including long speaker wires up to 100 cm and high power. The TPA3139D2 EVM passes FCC Class B specifications under these conditions using twisted speaker wires. The size and type of ferrite bead can be selected to meet application requirements. Also, the filter capacitor can be increased if necessary with some impact on efficiency.

There may be a few circuit instances where it is necessary to add a complete LC reconstruction filter. These circumstances might occur if there are nearby circuits which are sensitive to noise. In these cases a classic second order Butterworth filter similar to those shown in the figures below can be used.

Some systems have little power supply decoupling from the AC line but are also subject to line conducted interference (LCI) regulations. These include systems powered by "wall warts" and "power bricks." In these cases, LC reconstruction filters can be the lowest cost means to pass LCI tests. Common mode chokes using low frequency ferrite material can also be effective at preventing line conducted interference.
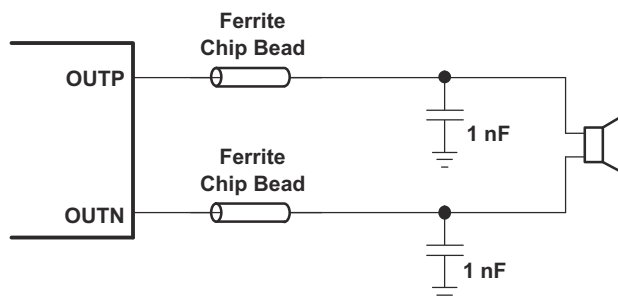

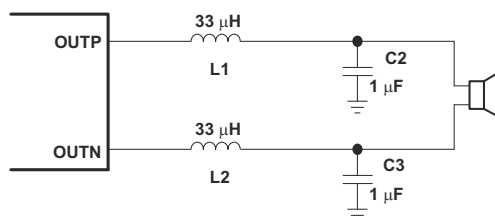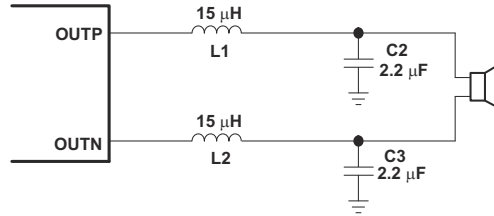図 8-3. Typical Ferrite Chip Bead Filter (Chip Bead Example: NFZ2MSM series from Murata)

図 8-4. Typical LC Output Filter, Cutoff Frequency of 27 kHz, Speaker Impedance = 8 Ω

図 8-5. Typical LC Output Filter, Cutoff Frequency of 27 kHz, Speaker Impedance = 6 Ω

8.2.2.4 Input Resistance

The typical input resistance of the amplifier is fixed to 20 kΩ ±15% for 26dB Gain and 40kΩ ±15% for 20dB Gain .
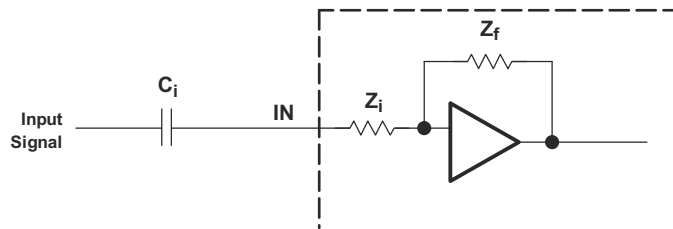
8.2.2.5 Input Capacitor, C_i

In the typical application, an input capacitor (C_i) is required to allow the amplifier to bias the input signal to the proper dc level for optimum operation. In this case, C_i and the input impedance of the amplifier (Z_i) form a high-pass filter with the corner frequency determined in 式 2.

$$f_c = \frac{1}{2\pi Z_i C_i}$$

(2)
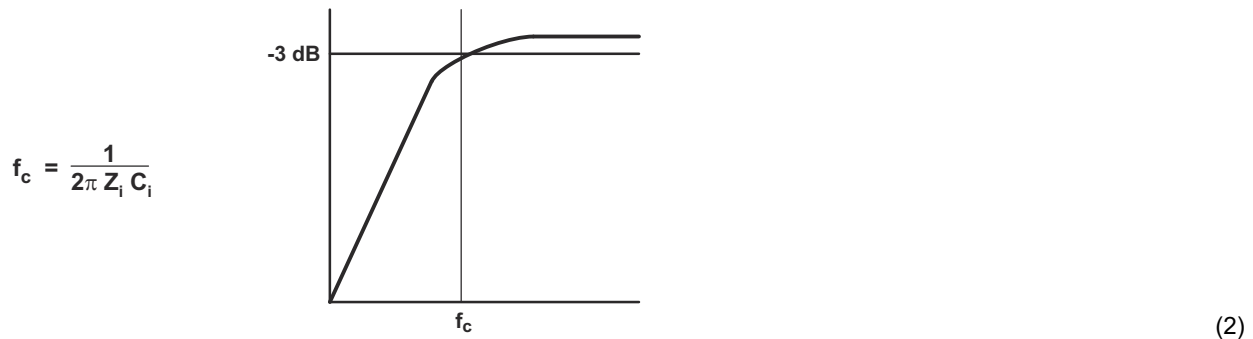
The value of C_i is important, as it directly affects the bass (low-frequency) performance of the circuit. Consider the example where Z_i is 20 kΩ (26dB Gain) and the specification calls for a flat bass response down to 20 Hz. 式 2 is reconfigured as 式 3.

$$C_i = \frac{1}{2\pi Z_i f_c}$$

(3)

In this example, C_i is 0.4 µF; so, one would likely choose a value of 0.39 µF as this value is commonly used. A further consideration for this capacitor is the leakage path from the input source through the input network (C_i) and the feedback network to the load. This leakage current creates a dc offset voltage at the input to the amplifier that reduces useful headroom. For this reason, a low-leakage tantalum or ceramic capacitor is the best choice. When polarized capacitors are used, the positive side of the capacitor should face the amplifier input in most applications as the dc level there is held at 3 V, which is likely higher than the source dc level. Note that it is important to confirm the capacitor polarity in the application. Additionally, lead-free solder can create dc offset voltages and it is important to ensure that boards are cleaned properly.

8.2.2.6 BSN and BSP Capacitors

The full H-bridge output stages use only NMOS transistors. Therefore, they require bootstrap capacitors for the high side of each output to turn on correctly. A 0.22-µF ceramic capacitor, rated for at least 25 V, must be connected from each output to its corresponding bootstrap input. Specifically, one 0.22-µF capacitor must be connected from OUTPx to BSPx, and one 0.22-µF capacitor must be connected from OUTNx to BSNx. (See the application circuit diagram in 図 8-1.)

The bootstrap capacitors connected between the BSxx pins and corresponding output function as a floating power supply for the high-side N-channel power MOSFET gate drive circuitry. During each high-side switching cycle, the bootstrap capacitors hold the gate-to-source voltage high enough to keep the high-side MOSFETs turned on.

8.2.2.7 Differential Inputs

The differential input stage of the amplifier cancels any noise that appears on both input lines of the channel. To use the TPA3139D2 device with a differential source, connect the positive lead of the audio source to the INP input and the negative lead from the audio source to the INN input. To use the TPA3139D2 with a single-ended source, ac ground the INP or INN input through a capacitor equal in value to the input capacitor on INN or INP and apply the audio source to either input. In a single-ended input application, the unused input should be ac grounded at the audio source instead of at the device input for best noise performance. For good transient performance, the impedance seen at each of the two differential inputs should be the same.

The impedance seen at the inputs should be limited to an RC time constant of 3 ms or less if possible. This is to allow the input dc blocking capacitors to become completely charged during the 50-ms power-up time. If the input capacitors are not allowed to completely charge, there is some additional sensitivity to component matching which can result in pop if the input components are not well matched.

8.2.2.8 Using Low-ESR Capacitors

Low-ESR capacitors are recommended throughout this application section. A real (as opposed to ideal) capacitor can be modeled simply as a resistor in series with an ideal capacitor. The voltage drop across this resistor minimizes the beneficial effects of the capacitor in the circuit. The lower the equivalent value of this resistance, the more the real capacitor behaves like an ideal capacitor.

8.2.3 Application Performance Curves

8.2.3.1 EN55013 Radiated Emissions Results

TPA3139D2 EVM, PVCC = 12 V, 8-Ω speakers, P_O = 4 W

図 8-6. Radiated Emission - Horizontal

図 8-7. Radiated Emission - Vertical
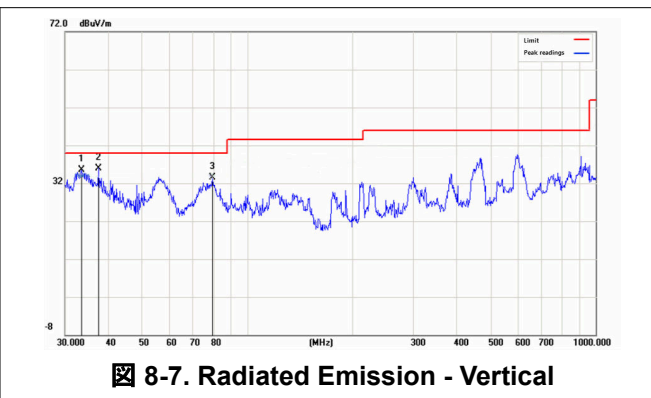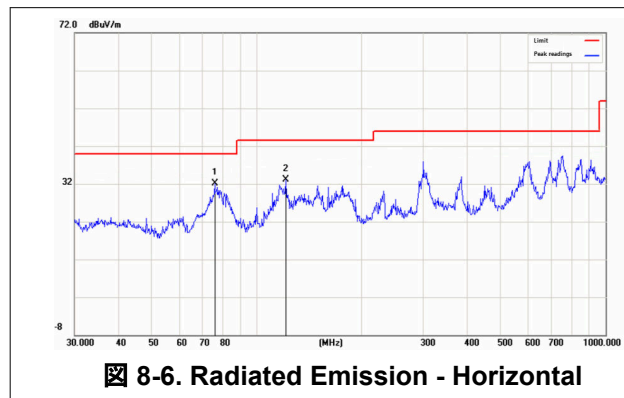
8.2.3.2 EN55022 Conducted Emissions Results

TPA3139D2 EVM, PVCC = 12 V, 8-Ω speakers, P_O = 4 W

図 8-8. Conducted Emission - Line

図 8-9. Conducted Emission - Neutral

Product Folder Links: *TPA3139D2*
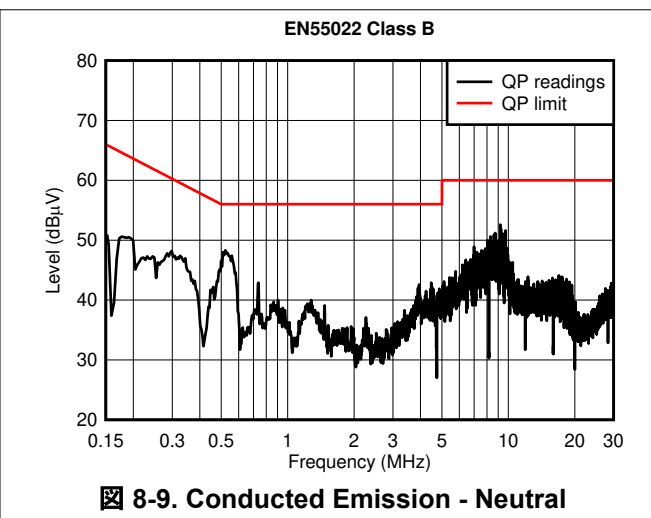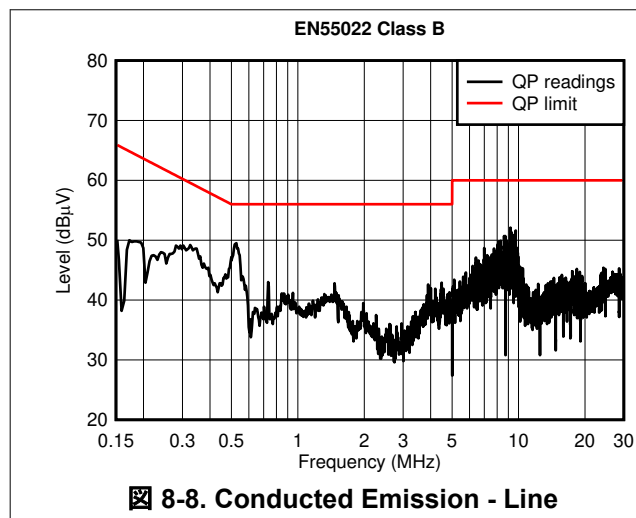
9 Power Supply Recommendations

9.1 Power Supply Decoupling, C$_S$

The TPA3139D2 device is a high-performance CMOS audio amplifier that requires adequate power supply decoupling to ensure that the output total harmonic distortion (THD) is as low as possible. Power supply decoupling also prevents oscillations for long lead lengths between the amplifier and the speaker. Optimum decoupling is achieved by using a network of capacitors of different types that target specific types of noise on the power supply leads. For higher frequency transients due to parasitic circuit elements such as bond wire and copper trace inductances as well as lead frame capacitance, a good quality low equivalent-series-resistance (ESR) ceramic capacitor of value between 220 pF and 1000 pF works well. This capacitor should be placed as close to the device PVCC pins and system ground (either GND pins or thermal pad) as possible. For mid-frequency noise due to filter resonances or PWM switching transients as well as digital hash on the line, another good quality capacitor typically 0.1 µF to 1 µF placed as close as possible to the device PVCC leads works best. For filtering lower frequency noise signals, a larger aluminum electrolytic capacitor of 100 µF or greater placed near the audio power amplifier is recommended. The 100-µF capacitor also serves as a local storage capacitor for supplying current during large signal transients on the amplifier outputs. The PVCC pins provide the power to the output transistors, so a 100-µF or larger capacitor should be placed on each PVCC pin. A 1-µF capacitor on the AVCC pin is adequate. Also, a small decoupling resistor between AVCC and PVCC can be used to keep high frequency class-D noise from entering the linear input amplifiers.
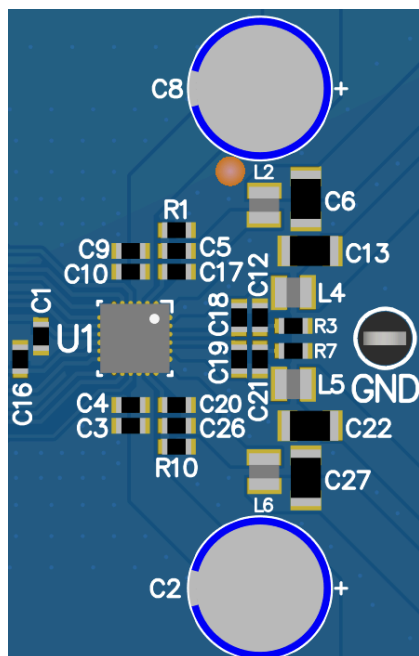
10 Layout

10.1 Layout Guidelines

The TPA3139D2 device can be used with a small, inexpensive ferrite bead output filter for most applications. However, since the Class-D switching edges are fast, it is necessary to take care when planning the layout of the printed circuit board. The following suggestions help meet EMC requirements.

- Decoupling capacitors—The high-frequency decoupling capacitors should be placed as close to the PVCC and AVCC pins as possible. Large (100-µF or greater) bulk power supply decoupling capacitors should be placed near the TPA3139D2 device on the PVCC supplies. Local, high-frequency bypass capacitors should be placed as close to the PVCC pins as possible. These caps can be connected to the thermal pad directly for an excellent ground connection. Consider adding a small, good quality low ESR ceramic capacitor between 220 pF and 1000 pF and a larger mid-frequency cap of value between 0.1 µF and 1 µF also of good quality to the PVCC connections at each end of the chip.
- Keep the current loop from each of the outputs through the ferrite bead and the small filter cap and back to GND as small and tight as possible. The size of this current loop determines its effectiveness as an antenna.
- Grounding—The AVCC decoupling capacitor should be connected to ground (GND). The PVCC decoupling capacitors should connect to GND. Analog ground and power ground should be connected at the thermal pad, which should be used as a central ground connection or star ground for the TPA3139D2.
- Output filter—The ferrite EMI filter (図 8-3) should be placed as close to the output pins as possible for the best EMI performance. The capacitors used in the ferrite should be grounded to power ground.
- Thermal Pad—The thermal pad must be soldered to the PCB for proper thermal performance and optimal reliability. The dimensions of the thermal pad and thermal land should be 3.04 mm × 2.34 mm. Seven rows of solid vias (three vias per row, 0.3302 mm or 13 mils diameter) should be equally spaced underneath the thermal land. The vias should connect to a solid copper plane, either on an internal layer or on the bottom layer of the PCB. The vias must be solid vias, not thermal relief or webbed vias. See the TI Application Report SCBA017D for more information about using the QFN thermal pad. For recommended PCB footprints, see figures at the end of this data sheet.

For an example layout, see the TPA3139D2 Evaluation Module (TPA3139D2EVM) User Manual. Both the EVM user manual and the thermal pad application report are available on the TI Web site at http://www.ti.com.
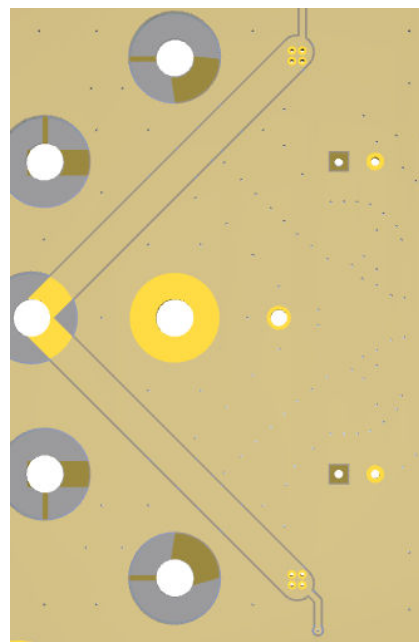
10.2 Layout Example
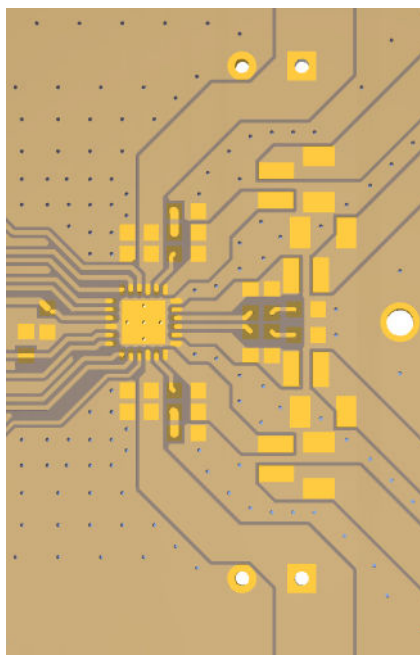
Top Layer 3D view   Top Layer layout view   Bot Layer layout view

図 10-1. BTL Layout Example

Product Folder Links: *TPA3139D2*

11 Device and Documentation Support

11.1 Device Support

11.1.1 Third-Party Products Disclaimer

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11.2 Documentation Support

11.2.1 Related Documentation

PowerPAD™ Thermally Enhanced Package Application Report (SLMA002)

11.3 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

11.4 Support Resources

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11.7 Glossary

TI Glossary   This glossary lists and explains terms, acronyms, and definitions.

Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package | Pins	Package qty | Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
TPA3139D2RGER	Active	Production	VQFN (RGE) | 24	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-10 to 85	TPA 3139D2
TPA3139D2RGER.A	Active	Production	VQFN (RGE) | 24	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-10 to 85	TPA 3139D2
TPA3139D2RGERG4	Active	Production	VQFN (RGE) | 24	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-10 to 85	TPA 3139D2
TPA3139D2RGERG4.A	Active	Production	VQFN (RGE) | 24	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-10 to 85	TPA 3139D2

(1) Status: For more details on status, see our product life cycle.

(2) Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

(4) Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.
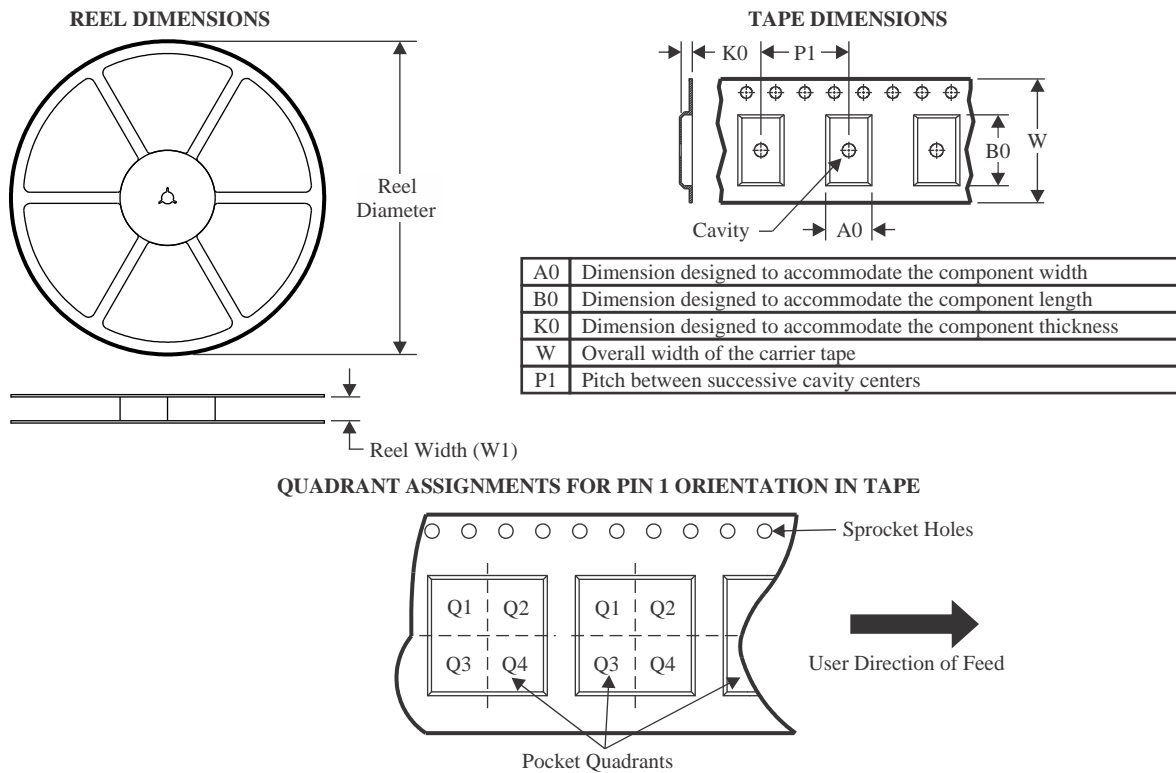
(6) Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

PACKAGE MATERIALS INFORMATION

TAPE AND REEL INFORMATION

REEL DIMENSIONS

TAPE DIMENSIONS

A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPA3139D2RGER	VQFN	RGE	24	3000	330.0	12.4	4.25	4.25	1.15	8.0	12.0	Q2
TPA3139D2RGERG4	VQFN	RGE	24	3000	330.0	12.4	4.25	4.25	1.15	8.0	12.0	Q2

TAPE AND REEL BOX DIMENSIONS
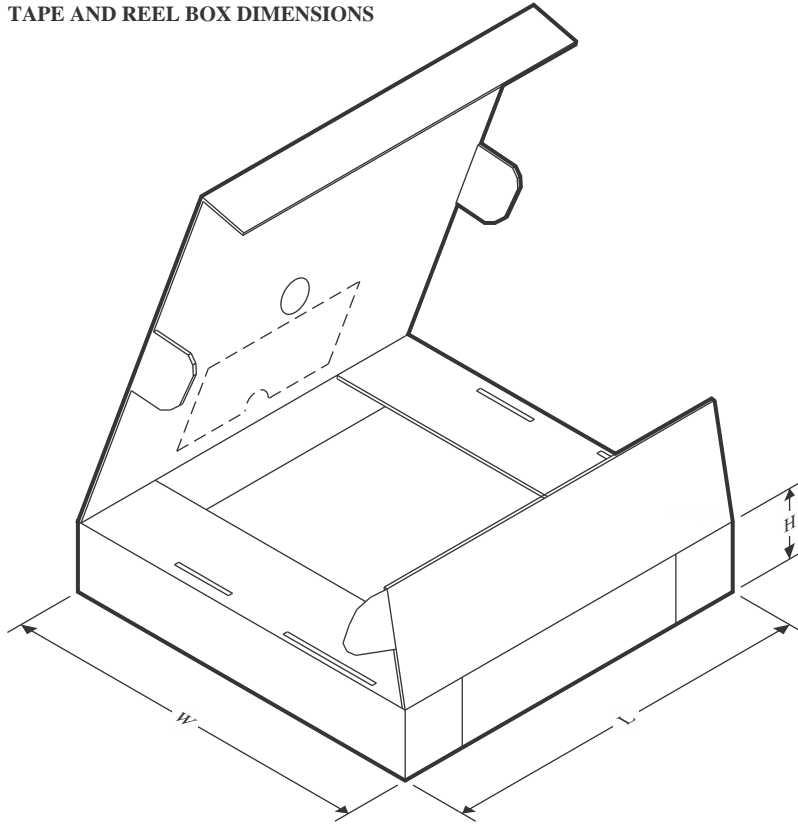
*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPA3139D2RGER	VQFN	RGE	24	3000	367.0	367.0	35.0
TPA3139D2RGERG4	VQFN	RGE	24	3000	367.0	367.0	35.0
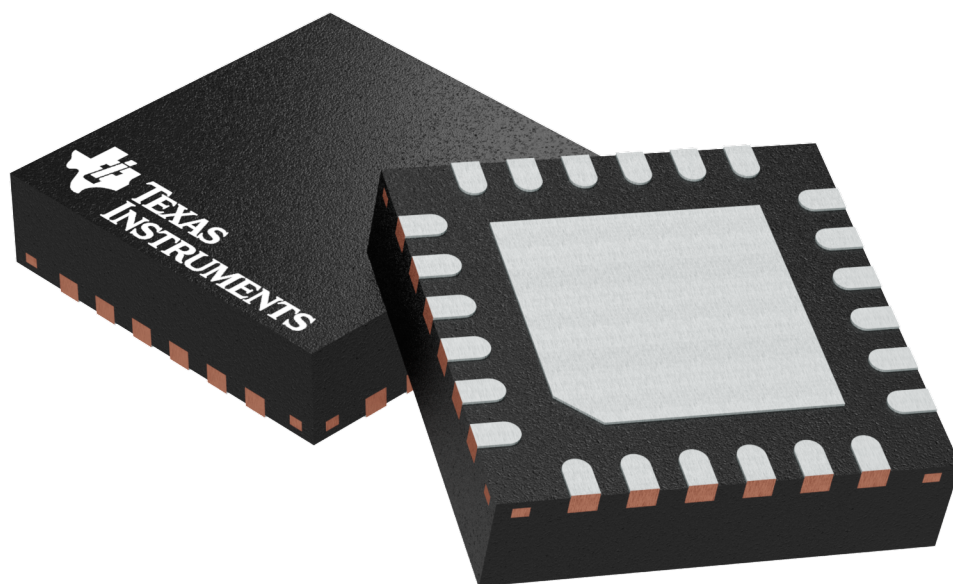
Images above are just a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.

4204104/H

TEXAS
INSTRUMENTS

B | 4.1 / 3.9 | A

PIN 1 INDEX AREA

4.1 / 3.9

1 MAX

0.05 / 0.00

C

SEATING PLANE

0.08 | C

☐ 2.7±0.1

2X 2.5

(0.2) TYP

7   12

20X 0.5

6

13

2X 2.5

25

SYMM ℄

1

18

PIN 1 ID (OPTIONAL)

24   19

SYMM ℄

24X 0.30 / 0.18

24X 0.48 / 0.28

⊕ | 0.1 Ⓜ | C | A | B
0.05 Ⓜ | C

4219016 / A   08/2017
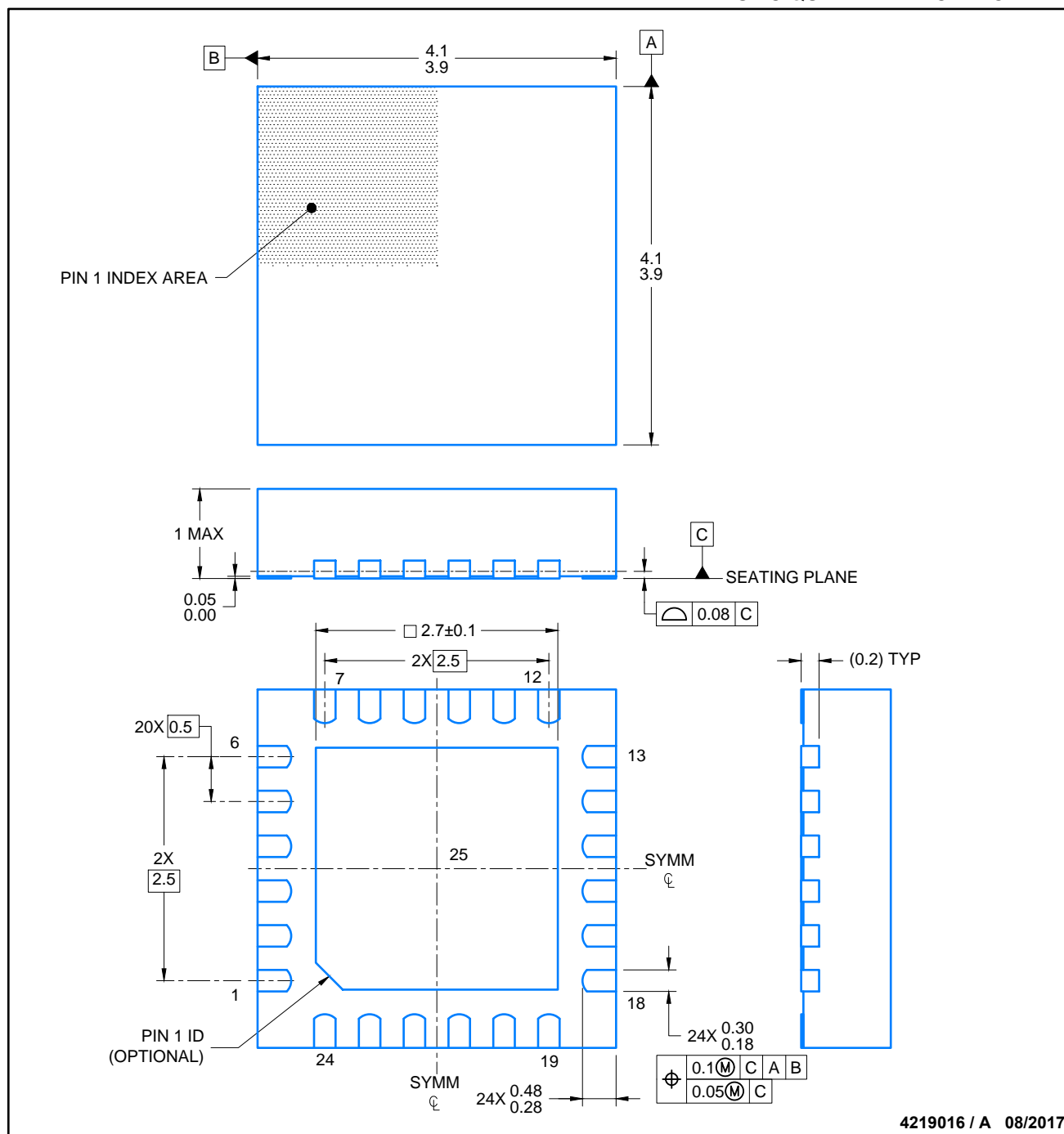
NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.

(3.825)

(□2.7)

24

19

24X (0.58)

24X (0.24)

1

20X (0.5)

18

SYMM

25

(3.825)

2X
(1.1)

(Ø0.2) VIA
TYP

6

13

(R0.05)

7

12

2X(1.1)

SYMM

LAND PATTERN EXAMPLE
SCALE: 20X

0.07 MAX
ALL AROUND

METAL

SOLDER MASK
OPENING

NON SOLDER MASK
DEFINED
(PREFERRED)

0.07 MIN
ALL AROUND

SOLDER MASK
OPENING

METAL UNDER
SOLDER MASK

SOLDER MASK
DEFINED

SOLDER MASK DETAILS

4219016 / A   08/2017

NOTES: (continued)

4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
5. Solder mask tolerances between and around signal pads can vary based on board fabrication site.
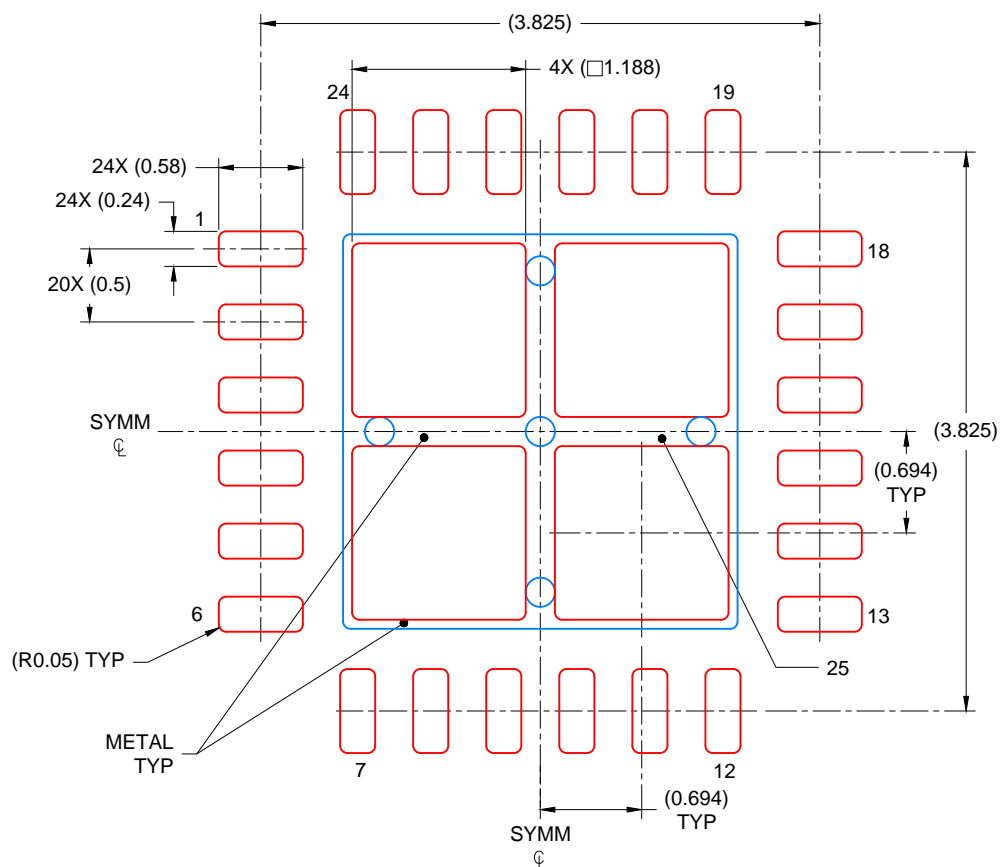
SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD
78% PRINTED COVERAGE BY AREA
SCALE: 20X

4219016 / A   08/2017

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations..

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